

## DRV870xD-Q1 汽车 半桥栅极驱动器

### 1 特性

- 符合汽车类应用的 AEC-Q100 标准
  - 器件温度 1 级:  $-40^{\circ}\text{C}$  至  $+125^{\circ}\text{C}$  的环境运行温度范围
- 单通道 半桥栅极驱动器
  - 驱动两个外部 N 通道 MOSFET
  - 支持 100% 脉宽调制 (PWM) 占空比
- 工作电源电压范围: 5.5V 至 45V
- PWM 控制接口
- 用于配置的串行接口 (DRV8703D-Q1)
- 用于转换率控制的可调栅极驱动器
- 支持 1.8V、3.3V 和 5V 逻辑输入
- 电流分流放大器
- 集成 PWM 电流调节功能
- 低功耗休眠模式
- 小型封装尺寸
  - 32 引脚 VQFN 封装
  - 5mm × 5mm
  - 可湿侧面封装
- DRV8303 中的特性
  - 电源欠压锁定 (UVLO)
  - 电荷泵欠压 (CPUV) 锁定
  - 过流保护 (OCP)
  - 栅极驱动器故障 (GDF)
  - 热关断 (TSD)
  - 监视器计时器 (DRV8703D-Q1)
  - 故障调节输出 (nFAULT)

### 2 应用

- 燃油泵
- 单向刷式直流电机
- 继电器或螺线管
- 单极负载

### 3 说明

DRV870xD-Q1 器件系列是一种半桥栅极驱动器，它使用两个外部 N 通道 MOSFET，旨在驱动单向刷式直流电机或螺线管负载。

PWM 接口允许轻松连接到控制器电路。内部感测放大器提供可调的电流控制。这款栅极驱动器内置有相应的电路，以便能够采用关断时间固定的 PWM 电流斩波来调节绕组电流。

DRV870xD-Q1 器件系列通过 10.5V  $V_{GS}$  栅极驱动器驱动高侧和低侧 FET。所有外部 FET 的栅极驱动电流都可通过单一外部电阻器或通过串行外设接口 (SPI) 进行配置。

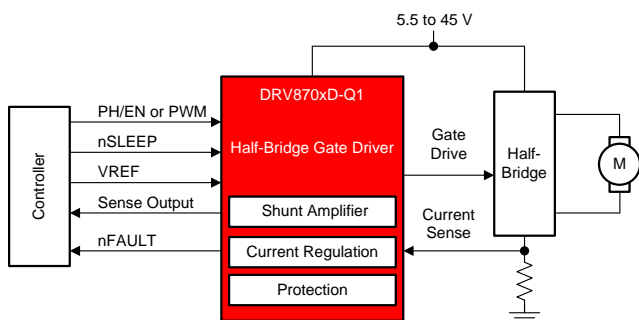
低功耗睡眠模式可将部分内部电路关断，从而实现极低的静态电流消耗。

#### 器件信息(1)

器件型号	封装	封装尺寸 (标称值)
DRV8702D-Q1	VQFN (32)	5.00mm × 5.00mm
DRV8703D-Q1		

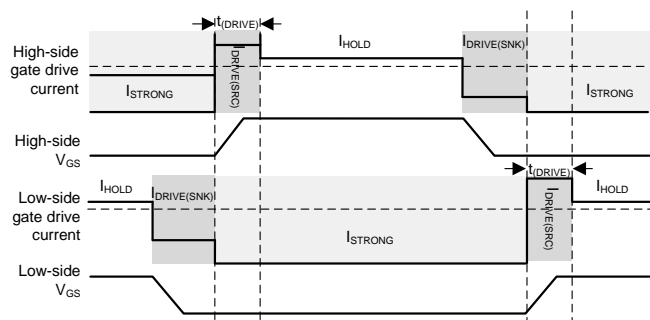
(1) 要了解所有可用封装，请参见数据表末尾的可订购产品附录。

#### 简化电路原理图



Copyright © 2017, Texas Instruments Incorporated

#### 栅极驱动电流



## 目录

<b>1</b>	特性 .....	<b>1</b>	7.6	Register Maps .....	<b>41</b>
<b>2</b>	应用 .....	<b>1</b>	<b>8</b>	<b>Application and Implementation</b> .....	<b>47</b>
<b>3</b>	说明 .....	<b>1</b>	8.1	Application Information.....	<b>47</b>
<b>4</b>	修订历史记录 .....	<b>2</b>	8.2	Typical Application .....	<b>47</b>
<b>5</b>	<b>Pin Configuration and Functions</b> .....	<b>3</b>	<b>9</b>	<b>Power Supply Recommendations</b> .....	<b>51</b>
<b>6</b>	<b>Specifications</b> .....	<b>5</b>	9.1	Bulk Capacitance Sizing .....	<b>51</b>
6.1	Absolute Maximum Ratings .....	<b>5</b>	<b>10</b>	<b>Layout</b> .....	<b>52</b>
6.2	ESD Ratings.....	<b>5</b>	10.1	Layout Guidelines .....	<b>52</b>
6.3	Recommended Operating Conditions.....	<b>6</b>	10.2	Layout Example .....	<b>52</b>
6.4	Thermal Information .....	<b>6</b>	<b>11</b>	<b>器件和文档支持</b> .....	<b>53</b>
6.5	Electrical Characteristics.....	<b>6</b>	11.1	文档支持 .....	<b>53</b>
6.6	SPI Timing Requirements .....	<b>11</b>	11.2	相关链接 .....	<b>53</b>
6.7	Switching Characteristics .....	<b>11</b>	11.3	接收文档更新通知 .....	<b>53</b>
6.8	Typical Characteristics .....	<b>13</b>	11.4	社区资源 .....	<b>53</b>
<b>7</b>	<b>Detailed Description</b> .....	<b>18</b>	11.5	商标 .....	<b>53</b>
7.1	Overview .....	<b>18</b>	11.6	静电放电警告 .....	<b>53</b>
7.2	Functional Block Diagram .....	<b>19</b>	11.7	Glossary .....	<b>53</b>
7.3	Feature Description.....	<b>21</b>	<b>12</b>	<b>机械、封装和可订购信息</b> .....	<b>54</b>
7.4	Device Functional Modes.....	<b>39</b>	12.1	Package Option Addendum .....	<b>58</b>
7.5	Programming.....	<b>39</b>			

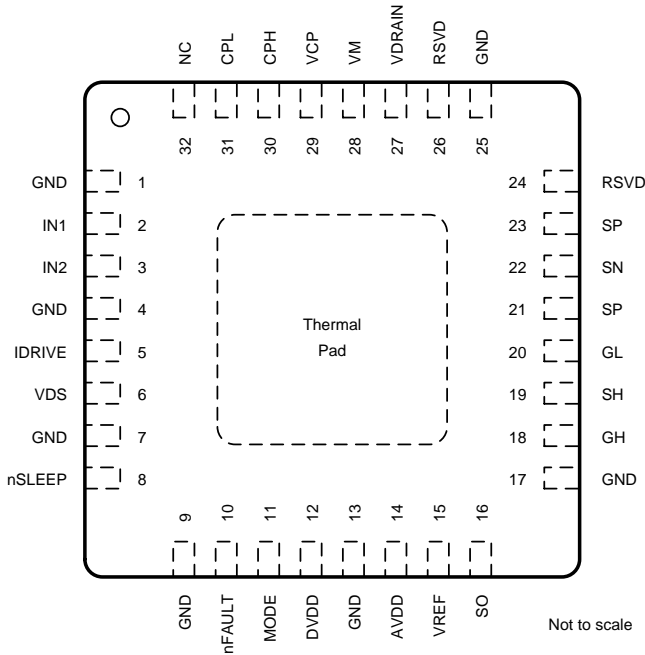
## 4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

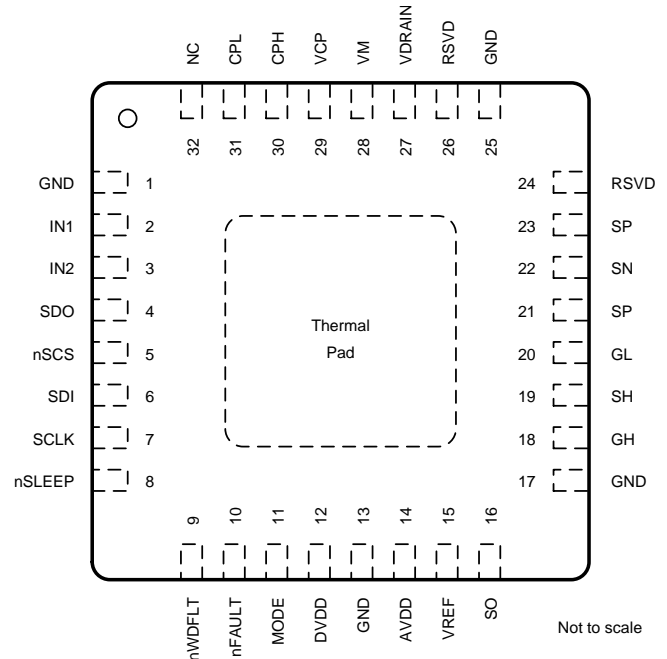
日期	修订版本	注释
2017 年 3 月	*	首次发布。

## 5 Pin Configuration and Functions

**DRV8702D-Q1 RHB Package With Wettable Flanks**  
32-Pin VQFN  
Top View



**DRV8703D-Q1 RHB Package With Wettable Flanks**  
32-Pin VQFN  
Top View



### Pin Functions

NAME	PIN NO.		TYPE <sup>(1)</sup>	DESCRIPTION
	DRV8702D-Q1	DRV8703D-Q1		
AVDD	14	14	PWR	Analog regulator. This pin is the 5-V analog supply regulator. Bypass this pin to ground with a 6.3-V, 1- $\mu$ F ceramic capacitor.
CPH	30	30	PWR	Charge-pump switching node. Connect a 0.1- $\mu$ F X7R capacitor rated for the supply voltage (VM) between the CPH and CPL pins.
CPL	31	31	PWR	Charge-pump switching node. Connect a 0.1- $\mu$ F X7R capacitor rated for the supply voltage (VM) between the CPH and CPL pins.
DVDD	12	12	PWR	Logic regulator. This pin is the regulator for the 3.3-V logic supply. Bypass this pin to ground with a 6.3-V, 1- $\mu$ F ceramic capacitor.
GH	18	18	O	High-side gate. Connect this pin to the high-side FET gate.
GL	20	20	O	Low-side gate. Connect this pin to the low-side FET gate.
GND	1	1	PWR	Device ground. Connect this pin to the system ground.
GND	13	13	PWR	Device ground. Connect this pin to the system ground.
GND	17	17	PWR	Device ground. Connect this pin to the system ground.
GND	25	25	PWR	Device ground. Connect this pin to the system ground.
GND	4	—	PWR	Device ground. Connect this pin to the system ground.
GND	7	—	PWR	Device ground. Connect this pin to the system ground.
GND	9	—	PWR	Device ground. Connect this pin to the system ground.
IDRIVE	5	—	I	Current setting pin for the gate drive. The resistor value or voltage forced on this pin sets the gate-drive current. For more information see the <a href="#">IDRIVE Configuration</a> section.
IN1	2	2	I	Input control pins. The logic of this pin is dependent on the MODE pin.
IN2	3	3	I	Input control pins. The logic of this pin is dependent on the MODE pin.

(1) I = input, O = output, PWR = power, NC = no connect, OD = open-drain output

**Pin Functions (continued)**

NAME	PIN		TYPE <sup>(1)</sup>	DESCRIPTION
	NO.			
	DRV8702D-Q1	DRV8703D-Q1		
MODE	11	11	I	Mode control pin. Pull this pin to logic high for half-bridge operation without internal current regulation. Leave this pin as no-connect for half-bridge operation with internal current regulation. Operation of this pin is latched on power up or when exiting sleep mode.
NC	32	32	NC	No connect. No internal connection
nFAULT	10	10	OD	Fault indication pin. This pin is pulled logic low when a fault condition occurs. This pin is an open-drain output that requires an external pullup resistor.
nSCS	—	5	I	SPI chip select. This pin is the select and enable for SPI. This pin is active low.
nSLEEP	8	8	I	Device sleep mode. Pull this pin to logic low to put device into a low-power sleep mode with the FETs in high impedance (Hi-Z). This pin is connected to an internal pulldown resistor.
nWDFLT	—	9	OD	Watchdog fault indication pin. This pin is pulled logic low when a watchdog fault condition occurs. This pin is an open-drain output that requires an external pullup resistor.
RSVD	26	26	RSVD	Reserved. Do not connect anything.
RSVD	24	24	RSVD	Reserved. Do not connect anything.
SCLK	—	7	I	SPI clock. This pin is for the SPI clock signal.
SDI	—	6	I	SPI input. This pin is for the SPI input signal.
SDO	—	4	OD	SPI output. This pin is for the SPI output signal. This pin is an open-drain output that requires an external pullup resistor.
SH	19	19	I	High-side source. Connect this pin to the high-side FET source.
SN	22	22	I	Shunt-amplifier negative input. Connect this pin to the current-sense resistor.
SO	16	16	O	Shunt-amplifier output. The voltage on this pin is equal to the SP voltage times $A_V$ plus an offset. Place no more than 1 nF of capacitance on this pin.
SP	21	21	I	Shunt-amplifier positive input. Connect this pin to the current-sense resistor.
SP	23	23	I	Shunt-amplifier positive input. Connect this pin to the current-sense resistor.
VCP	29	29	PWR	Charge-pump output. Connect a 16-V, 1- $\mu$ F ceramic capacitor between this pin and the VM pin.
VDRAIN	27	27	I	High-side FET drain connection. This pin is common for the half-bridge.
VDS	6	—	I	VDS monitor setting pin. The resistor value or voltage forced on this pin sets the VDS monitor threshold. For more information see the <a href="#">VDS Configuration</a> section.
VM	28	28	PWR	Power supply. Connect this pin to the motor supply voltage. Bypass this pin to ground with a 0.1- $\mu$ F ceramic plus a 10- $\mu$ F (minimum) capacitor.
VREF	15	15	I	Current set reference input. The voltage on this pin sets the driver chopping current.

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
Power supply voltage	VM	-0.3	47	V
Charge pump voltage	VCP, CPH	-0.3	V <sub>VM</sub> + 12	V
Charge pump negative switching pin	CPL	-0.3	V <sub>VM</sub>	V
Internal logic regulator voltage	DVDD	-0.3	3.8	V
Internal analog regulator voltage	AVDD	-0.3	5.75	V
Drain pin voltage	VDRAIN	-0.3	47	V
Voltage difference between supply and VDRAIN	VM – VDRAIN	-10	10	V
Control pin voltage	IN1, IN2, nSLEEP, nFAULT, VREF, IDRIVE, VVDS, MODE, nSCS, SCLK, SDI, SDO, nWDFLT	-0.3	5.75	V
High-side gate pin voltage	GH	-0.3	V <sub>VM</sub> + 12	V
Low-side gate pin voltage	GL	-0.3	12	V
Continuous phase-node pin voltage	SH	-1.2	V <sub>VM</sub> + 1.2	V
Pulsed 10-μs phase-node pin voltage	SH	-2	V <sub>VM</sub> + 2	V
Continuous shunt amplifier input pin voltage	SP	-0.5	1	V
	SN	-0.3	0.3	V
Pulsed 10-μs shunt amplifier input pin voltage	SP	-1	1	V
Shunt amplifier output pin voltage	SO	-0.3	5.75	V
Shunt amplifier output pin current	SO	0	5	mA
Maximum current, limit current with external series resistor	VDRAIN	-2	2	mA
Open-drain output current	nFAULT, SDO, nWDFLT	0	10	mA
Gate pin source current	GH, GL	0	250	mA
Gate pin sink current	GH, GL	0	500	mA
Operating junction temperature, T <sub>J</sub>		-40	150	°C
Storage temperature, T <sub>stg</sub>		-65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### 6.2 ESD Ratings

		VALUE	UNIT
V <sub>(ESD)</sub> Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 <sup>(1)</sup>		±2000
	Charged-device model (CDM), per AEC Q100-011	All pins	±500
		Corner pins (1, 8, 9, 16, 17, 24, 25, and 32)	±750

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

### 6.3 Recommended Operating Conditions

			MIN	MAX	UNIT
V <sub>VM</sub>	Power supply voltage	VM	5.5	45	V
V <sub>CC</sub>	Logic-level input voltage		0	5.25	V
V <sub>VREF</sub>	Reference root-mean-square (rms) voltage	VREF	0.3 <sup>(1)</sup>	3.6	V
f <sub>(PWM)</sub>	Applied PWM signal (IN1/IN2)	IN1, IN2		100	kHz
I <sub>AVDD</sub>	AVDD external load current			30 <sup>(2)</sup>	mA
I <sub>DVDD</sub>	DVDD external load current			30 <sup>(2)</sup>	mA
I <sub>SO</sub>	Shunt-amplifier output-current loading	SO		5	mA
T <sub>A</sub>	Operating ambient temperature		-40	125	°C

(1) Operational at V<sub>VREF</sub> = 0 to approximately 0.3 V, but accuracy is degraded.

(2) Power dissipation and thermal limits must be observed.

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		DRV870xD-Q1	UNIT
		RHB (VQFN)	
		32 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	32.9	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	19.6	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	6.8	°C/W
ψ <sub>JT</sub>	Junction-to-top characterization parameter	0.3	°C/W
ψ <sub>JB</sub>	Junction-to-board characterization parameter	6.8	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	1.8	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

### 6.5 Electrical Characteristics

Over recommended operating conditions unless otherwise noted. Typical limits apply for T<sub>A</sub> = 25°C and V<sub>VM</sub> = 13.5 V

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
<b>POWER SUPPLIES (VM, AVDD, DVDD)</b>						
V <sub>VM</sub>	VM operating voltage	Gate drivers functional	5.5	45	V	
		Logic functional	4.5	45		
I <sub>VM</sub>	VM operating supply current	V <sub>VM</sub> = 13.5 V; nSLEEP=1	5.5	7.5	12	mA
I <sub>(SLEEP)</sub>	VM sleep mode supply current	nSLEEP = 0, V <sub>VM</sub> = 13.5 V, T <sub>A</sub> = 25°C			14	μA
		nSLEEP = 0, V <sub>VM</sub> = 13.5 V, T <sub>A</sub> = 125°C <sup>(1)</sup>			25	
V <sub>DVDD</sub>	Internal logic regulator voltage	2-mA load	3	3.3	3.5	V
		30-mA load, V <sub>VM</sub> = 13.5 V	2.9	3.2	3.5	
V <sub>AVDD</sub>	Internal logic regulator voltage	2-mA load	4.7	5	5.3	V
		30-mA load, V <sub>VM</sub> = 13.5 V	4.6	5	5.3	
<b>CHARGE PUMP (VCP, CPH, CPL)</b>						
V <sub>VCP</sub>	VCP operating voltage	V <sub>VM</sub> = 13.5 V; I <sub>VCP</sub> = 0 to 12 mA	22.5	23.5	24.5	V
		V <sub>VM</sub> = 8 V; I <sub>VCP</sub> = 0 to 10 mA	13.7	14	14.8	
		V <sub>VM</sub> = 5.5 V; I <sub>VCP</sub> = 0 to 8 mA	8.9	9.1	9.5	
I <sub>VCP</sub>	Charge-pump current capacity	V <sub>VM</sub> > 13.5 V	12			mA
		8 V < V <sub>VM</sub> < 13.5 V	10			
		5.5 V < V <sub>VM</sub> < 8 V	8			
<b>CONTROL INPUTS (IN1, IN2, nSLEEP, MODE, nSCS, SCLK, SDI)</b>						
V <sub>IL</sub>	Input logic-low voltage		0	0.8	V	
V <sub>IH</sub>	Input logic-high voltage		1.5	5.25	V	

(1) Ensured by design and characterization data.

## Electrical Characteristics (continued)

Over recommended operating conditions unless otherwise noted. Typical limits apply for  $T_A = 25^\circ\text{C}$  and  $V_{VM} = 13.5\text{ V}$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{hys}$	Input logic hysteresis		100			mV
$I_{IL}$	Input logic-low current	$V_{IN} = 0\text{ V}$	-5		5	$\mu\text{A}$
$I_{IH}$	Input logic-high current	$V_{IN} = 5\text{ V}$			70	$\mu\text{A}$
$R_{PD}$	Pulldown resistance		64	100	173	$\text{k}\Omega$
<b>CONTROL OUTPUTS (nFAULT, nWDFLT, SDO)</b>						
$V_{OL}$	Output logic-low voltage	$I_O = 2\text{ mA}$			0.1	V
$I_{OZ}$	Output high-impedance leakage	5V pullup voltage	-2		2	$\mu\text{A}$
<b>FET GATE DRIVERS (GH, SH, GL)</b>						
$V_{GSH}$	High-side $V_{GS}$ gate drive (gate-to-source)	$V_{VM} > 13.5\text{ V}$ ; $V_{GSH}$ with respect to SH		10.5	11.5	V
		$V_{VM} = 8\text{ V}$ ; $V_{GSH}$ with respect to SH		5.7	6.8	
		$V_{VM} = 5.5\text{ V}$ ; $V_{GSH}$ with respect to SH		3.4	4	
$V_{GSL}$	Low-side $V_{GS}$ gate drive (gate-to-source)	$V_{VM} > 10.5\text{ V}$		10.5		V
		$V_{VM} < 10.5\text{ V}$		$V_{VM} - 2$		
$I_{DRIVE(SRC\_HS)}$	High-side peak source current ( $V_{VM} = 5.5\text{V}$ )	$R_{(IDRIVE)} < 1\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b000 (DRV8703D)		10		mA
		$R_{(IDRIVE)} = 33\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b001 (DRV8703D)		20		
		$R_{(IDRIVE)} = 200\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b010 (DRV8703D)		50		
		IDRIVE = 3'b011 (DRV8703D)		70		
		IDRIVE = 3'b100 (DRV8703D)		100		
		$R_{(IDRIVE)} > 2\text{ M}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b101 (DRV8703D)		145		
		$R_{(IDRIVE)} = 68\text{ k}\Omega$ to AVDD (DRV8702D) or IDRIVE = 3'b110 (DRV8703D)		190		
		$R_{(IDRIVE)} = 1\text{ k}\Omega$ to AVDD (DRV8702D) or IDRIVE = 3'b111 (DRV8703D)		240		
$I_{DRIVE(SNK\_HS)}$	High-side peak sink current ( $V_{VM} = 5.5\text{V}$ )	$R_{(IDRIVE)} < 1\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b000 (DRV8703D)		20		mA
		$R_{(IDRIVE)} = 33\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b001 (DRV8703D)		40		
		$R_{(IDRIVE)} = 200\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b010 (DRV8703D)		90		
		IDRIVE = 3'b011 (DRV8703D)		120		
		IDRIVE = 3'b100 (DRV8703D)		170		
		$R_{(IDRIVE)} > 2\text{ M}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b101 (DRV8703D)		250		
		$R_{(IDRIVE)} = 68\text{ k}\Omega$ to AVDD (DRV8702D) or IDRIVE = 3'b110 (DRV8703D)		330		
		$R_{(IDRIVE)} = 1\text{ k}\Omega$ to AVDD (DRV8702D) or IDRIVE = 3'b111 (DRV8703D)		420		

**Electrical Characteristics (continued)**

 Over recommended operating conditions unless otherwise noted. Typical limits apply for  $T_A = 25^\circ\text{C}$  and  $V_{VM} = 13.5\text{ V}$ 

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
$I_{\text{DRIVE(SRC\_LS)}}$ Low-side peak source current ( $V_{VM} = 5.5\text{V}$ )	$R_{(\text{IDRIVE})} < 1\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b000 (DRV8703D)		10		mA
	$R_{(\text{IDRIVE})} = 33\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b001 (DRV8703D)		20		
	$R_{(\text{IDRIVE})} = 200\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b010 (DRV8703D)		40		
	IDRIVE = 3'b011 (DRV8703D)		55		
	IDRIVE = 3'b100 (DRV8703D)		75		
	$R_{(\text{IDRIVE})} > 2\text{ M}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b101 (DRV8703D)		115		
	$R_{(\text{IDRIVE})} = 68\text{ k}\Omega$ to AVDD (DRV8702D) or IDRIVE = 3'b110 (DRV8703D)		145		
	$R_{(\text{IDRIVE})} = 1\text{ k}\Omega$ to AVDD (DRV8702D) or IDRIVE = 3'b111 (DRV8703D)		190		
$I_{\text{DRIVE(SNK\_LS)}}$ Low-side peak sink current ( $V_{VM} = 5.5\text{V}$ )	$R_{(\text{IDRIVE})} < 1\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b000 (DRV8703D)		20		mA
	$R_{(\text{IDRIVE})} = 33\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b001 (DRV8703D)		40		
	$R_{(\text{IDRIVE})} = 200\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b010 (DRV8703D)		85		
	IDRIVE = 3'b011 (DRV8703D)		115		
	IDRIVE = 3'b100 (DRV8703D)		160		
	$R_{(\text{IDRIVE})} > 2\text{ M}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b101 (DRV8703D)		235		
	$R_{(\text{IDRIVE})} = 68\text{ k}\Omega$ to AVDD (DRV8702D) or IDRIVE = 3'b110 (DRV8703D)		300		
	$R_{(\text{IDRIVE})} = 1\text{ k}\Omega$ to AVDD (DRV8702D) or IDRIVE = 3'b111 (DRV8703D)		360		
$I_{\text{DRIVE(SRC\_HS)}}$ High-side peak source current ( $V_{VM} = 13.5\text{V}$ )	$R_{(\text{IDRIVE})} < 1\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b000 (DRV8703D)		10		mA
	$R_{(\text{IDRIVE})} = 33\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b001 (DRV8703D)		20		
	$R_{(\text{IDRIVE})} = 200\text{ k}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b010 (DRV8703D)		50		
	IDRIVE = 3'b011 (DRV8703D)		70		
	IDRIVE = 3'b100 (DRV8703D)		105		
	$R_{(\text{IDRIVE})} > 2\text{ M}\Omega$ to GND (DRV8702D) or IDRIVE = 3'b101 (DRV8703D)		155		
	$R_{(\text{IDRIVE})} = 68\text{ k}\Omega$ to AVDD (DRV8702D) or IDRIVE = 3'b110 (DRV8703D)		210		
	$R_{(\text{IDRIVE})} = 1\text{ k}\Omega$ to AVDD (DRV8702D) or IDRIVE = 3'b111 (DRV8703D)		260		



**Electrical Characteristics (continued)**

Over recommended operating conditions unless otherwise noted. Typical limits apply for  $T_A = 25^\circ\text{C}$  and  $V_{VM} = 13.5\text{ V}$ 

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$I_{\text{DRIVE(SNK_HS)}}$	High-side peak sink current ( $V_{VM} = 13.5\text{V}$ )	$R_{(\text{IDRIVE})} < 1\text{ k}\Omega$ to GND (DRV8702D) or $\text{IDRIVE} = 3'b000$ (DRV8703D)		20		mA
		$R_{(\text{IDRIVE})} = 33\text{ k}\Omega$ to GND (DRV8702D) or $\text{IDRIVE} = 3'b001$ (DRV8703D)		40		
		$R_{(\text{IDRIVE})} = 200\text{ k}\Omega$ to GND (DRV8702D) or $\text{IDRIVE} = 3'b010$ (DRV8703D)		95		
		$\text{IDRIVE} = 3'b011$ (DRV8703D)		130		
		$\text{IDRIVE} = 3'b100$ (DRV8703D)		185		
		$R_{(\text{IDRIVE})} > 2\text{ M}\Omega$ to GND (DRV8702D) or $\text{IDRIVE} = 3'b101$ (DRV8703D)		265		
		$R_{(\text{IDRIVE})} = 68\text{ k}\Omega$ to AVDD (DRV8702D) or $\text{IDRIVE} = 3'b110$ (DRV8703D)		350		
		$R_{(\text{IDRIVE})} = 1\text{ k}\Omega$ to AVDD (DRV8702D) or $\text{IDRIVE} = 3'b111$ (DRV8703D)		440		
$I_{\text{DRIVE(SRC_LS)}}$	Low-side peak source current ( $V_{VM} = 13.5\text{V}$ )	$R_{(\text{IDRIVE})} < 1\text{ k}\Omega$ to GND (DRV8702D) or $\text{IDRIVE} = 3'b000$ (DRV8703D)		10		mA
		$R_{(\text{IDRIVE})} = 33\text{ k}\Omega$ to GND (DRV8702D) or $\text{IDRIVE} = 3'b001$ (DRV8703D)		20		
		$R_{(\text{IDRIVE})} = 200\text{ k}\Omega$ to GND (DRV8702D) or $\text{IDRIVE} = 3'b010$ (DRV8703D)		45		
		$\text{IDRIVE} = 3'b011$ (DRV8703D)		60		
		$\text{IDRIVE} = 3'b100$ (DRV8703D)		90		
		$R_{(\text{IDRIVE})} > 2\text{ M}\Omega$ to GND (DRV8702D) or $\text{IDRIVE} = 3'b101$ (DRV8703D)		130		
		$R_{(\text{IDRIVE})} = 68\text{ k}\Omega$ to AVDD (DRV8702D) or $\text{IDRIVE} = 3'b110$ (DRV8703D)		180		
		$R_{(\text{IDRIVE})} = 1\text{ k}\Omega$ to AVDD (DRV8702D) or $\text{IDRIVE} = 3'b111$ (DRV8703D)		225		
$I_{\text{DRIVE(SNK_LS)}}$	Low-side peak sink current ( $V_{VM} = 13.5\text{V}$ )	$R_{(\text{IDRIVE})} < 1\text{ k}\Omega$ to GND (DRV8702D) or $\text{IDRIVE} = 3'b000$ (DRV8703D)		20		mA
		$R_{(\text{IDRIVE})} = 33\text{ k}\Omega$ to GND (DRV8702D) or $\text{IDRIVE} = 3'b001$ (DRV8703D)		40		
		$R_{(\text{IDRIVE})} = 200\text{ k}\Omega$ to GND (DRV8702D) or $\text{IDRIVE} = 3'b010$ (DRV8703D)		95		
		$\text{IDRIVE} = 3'b011$ (DRV8703D)		125		
		$\text{IDRIVE} = 3'b100$ (DRV8703D)		180		
		$R_{(\text{IDRIVE})} > 2\text{ M}\Omega$ to GND (DRV8702D) or $\text{IDRIVE} = 3'b101$ (DRV8703D)		260		
		$R_{(\text{IDRIVE})} = 68\text{ k}\Omega$ to AVDD (DRV8702D) or $\text{IDRIVE} = 3'b110$ (DRV8703D)		350		
		$R_{(\text{IDRIVE})} = 1\text{ k}\Omega$ to AVDD (DRV8702D) or $\text{IDRIVE} = 3'b111$ (DRV8703D)		430		
$I_{\text{HOLD}}$	FET holding current	Source current after $t_{\text{DRIVE}}$		10		mA
		Sink current after $t_{\text{DRIVE}}$		40		
$I_{\text{STRONG}}$	FET holdoff strong pulldown	GH		750		mA
		GL		1000		
$R_{(\text{OFF})}$	FET gate holdoff resistor	Pulldown GH to SH		150		k $\Omega$
		Pulldown GL to GND		150		
<b>CURRENT SHUNT AMPLIFIER AND PWM CURRENT CONTROL (SP, SN, SO, VREF)</b>						
$V_{\text{VREF}}$	VREF input rms voltage	For current internal chopping		0.3 <sup>(2)</sup>	3.6	V

(2) Operational at  $V_{\text{VREF}} = 0$  to approximately 0.3 V, but accuracy is degraded.

**Electrical Characteristics (continued)**

 Over recommended operating conditions unless otherwise noted. Typical limits apply for  $T_A = 25^\circ\text{C}$  and  $V_{VM} = 13.5\text{ V}$ 

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$R_{VREF}$	VREF input impedance	DRV8702D and DRV8703D VREF_SCL = 00 (100%)	1			M $\Omega$
		DRV8703D VREF_SCL = 2'b01, 2'b10 or 2'b11		175		k $\Omega$
$A_V$	Amplifier gain (DRV8702D-Q1)	$60 < V_{SP} < 225\text{ mV}$ ; $V_{SN} = \text{GND}$	19.3	19.8	20.3	V/V
$A_V$	Amplifier gain (DRV8703D-Q1)	GAIN_CS = 00; $10 < V_{SP} < 450\text{ mV}$ ; $V_{SN} = \text{GND}$	9.75	10	10.25	V/V
		GAIN_CS = 01; $60 < V_{SP} < 225\text{ mV}$ ; $V_{SN} = \text{GND}$	19.3	19.8	20.3	
		GAIN_CS = 10; $10 < V_{SP} < 112\text{ mV}$ ; $V_{SN} = \text{GND}$	38.4	39.4	40.4	
		GAIN_CS = 11; $10 < V_{SP} < 56\text{ mV}$ ; $V_{SN} = \text{GND}$	73	78	81	
$V_{IO}$	Input-referred offset	$V_{SP} = V_{SN} = \text{GND}$		5	10	mV
$V_{IO(DRIFT)}$	Drift offset <sup>(2)</sup>	$V_{SP} = V_{SN} = \text{GND}$		10		$\mu\text{V}/^\circ\text{C}$
$I_{SP}$	SP input current	$V_{SP} = 100\text{ mV}$ ; $V_{SN} = \text{GND}$		-20		$\mu\text{A}$
$V_{SO}$	SO pin output voltage range		$A_V \times V_{OFF}$		4.5	V
$C_{(SO)}$	Allowable SO pin capacitance				1	nF
<b>PROTECTION CIRCUITS</b>						
$V_{(UVLO2)}$	VM undervoltage lockout	VM falling; UVLO2 report		5.25	5.45	V
		VM rising; UVLO2 recovery		5.4	5.65	
$V_{(UVLO1)}$	Logic undervoltage lockout				4.5	V
$V_{hys(UVLO)}$	VM undervoltage hysteresis	Rising to falling threshold	100			mV
$V_{(CP\_UV)}$	Charge pump undervoltage	VCP falling; CPUV report		$V_{VM} + 1.5$		V
		VCP rising; CPUV recovery		$V_{VM} + 1.55$		
$V_{hys(CP\_UV)}$	CP undervoltage hysteresis	Rising to falling threshold		50		mV
$V_{(DS\_OCP)}$	Overcurrent protection trip level, $V_{DS}$ of each external FET (DRV8702D-Q1) High side FETs: VDRAIN – SH Low side FETs: SH – SP	$R_{(VDS)} < 1\text{ k}\Omega$ to GND		0.06		V
		$R_{(VDS)} = 33\text{ k}\Omega$ to GND		0.12		
		$R_{(VDS)} = 200\text{ k}\Omega$ to GND		0.24		
		$R_{(VDS)} > 2\text{ M}\Omega$ to GND		0.48		
		$R_{(VDS)} = 68\text{ k}\Omega$ to AVDD		0.96		
		$R_{(VDS)} < 1\text{ k}\Omega$ to AVDD		Disabled		
$V_{(DS\_OCP)}$	Overcurrent protection trip level, $V_{DS}$ of each external FET (DRV8703D-Q1) High-side FETs: VDRAIN – SH Low-side FETs: SH – SP	VDS_LEVEL = 3'b000		0.06		V
		VDS_LEVEL = 3'b001		0.145		
		VDS_LEVEL = 3'b010		0.17		
		VDS_LEVEL = 3'b011		0.2		
		VDS_LEVEL = 3'b100		0.12		
		VDS_LEVEL = 3'b101		0.24		
		VDS_LEVEL = 3'b110		0.48		
		VDS_LEVEL = 3'b111		0.96		
$V_{(SP\_OCP)}$	Overcurrent protection trip level, measured by sense amplifier	$V_{SP}$ with respect to GND	0.8	1	1.2	V
$T_{(OTW)}$	Thermal warning temperature <sup>(1)</sup>	Die temperature $T_J$	120	135	145	$^\circ\text{C}$
$T_{SD}$	Thermal shutdown temperature <sup>(1)</sup>	Die temperature $T_J$	150			$^\circ\text{C}$
$T_{hys}$	Thermal shutdown hysteresis <sup>(1)</sup>	Die temperature $T_J$		20		$^\circ\text{C}$
$V_{C(GS)}$	Gate-drive clamping voltage	Positive clamping voltage	16.3	17	17.8	V
		Negative clamping voltage	-1	-0.7	-0.5	

## 6.6 SPI Timing Requirements

		MIN	NOM	MAX	UNIT
$t_{(CLK)}$	Minimum SPI clock period	100			ms
$t_{(CLKH)}$	Clock high time	50			ns
$t_{(CLKL)}$	Clock low time	50			ns
$t_{su(SDI)}$	SDI input data setup time	20			ns
$t_h(SDI)$	SDI input data hold time	30			ns
$t_h(SDO)$	SDO output hold time	40			ns
$t_{su(SCS)}$	SCS setup time	50			ns
$t_h(SCS)$	SCS hold time	50			ns
$t_{(HL\_SCS)}$	SCS minimum high time before SCS active low	400			ns

## 6.7 Switching Characteristics

Over recommended operating conditions unless otherwise noted

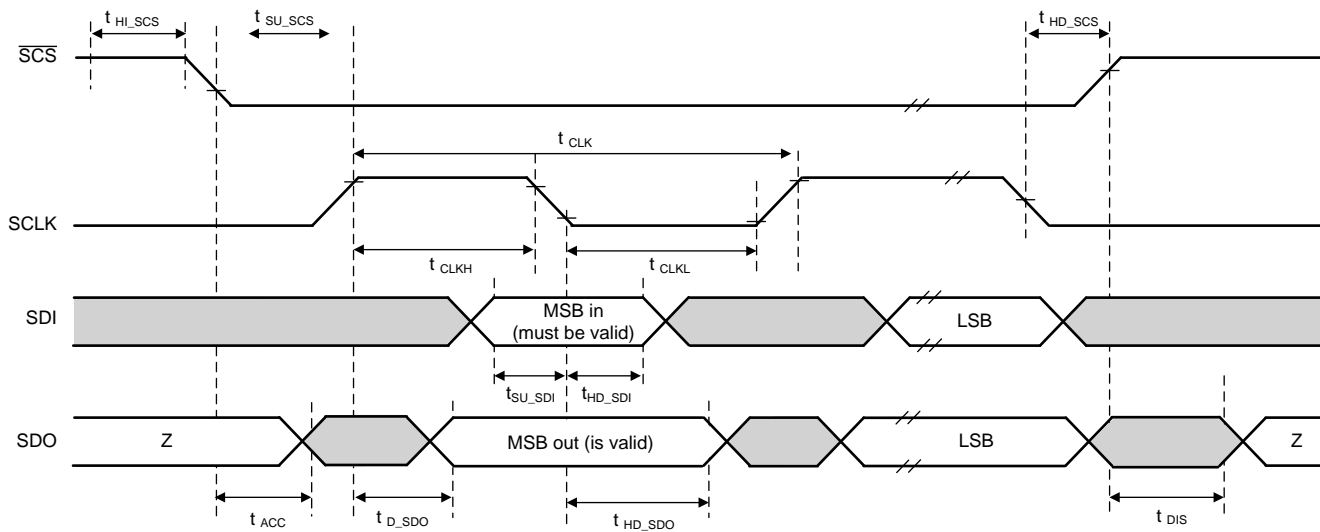
PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT			
<b>POWER SUPPLIES (VM, AVDD, DVDD)</b>								
$t_{(SLEEP)}$	Sleep time	nSLEEP = low to sleep mode			100	$\mu$ s		
$t_{(wu)}$	Wake-up time	nSLEEP = high to output change			1	ms		
$t_{on}$	Turnon time	VM > UVLO2 to output transition			1	ms		
<b>CHARGE PUMP (VCP, CPH, CPL)</b>								
$f_{S(VCP)}$	Charge-pump switching frequency	VM > UVLO2			200	400	700	kHz
<b>CONTROL INPUTS (IN1, IN2, nSLEEP, MODE, nSCS, SCLK, SDI)</b>								
$t_{pd}$	Propagation delay	IN1, IN2 or PH, EN to GH or GL			500		ns	
<b>FET GATE DRIVERS (GH, GH, SH, SH, GL, GL)</b>								
$t_{(DEAD)}$	Output dead time (DRV8702D-Q1)	Observed $t_{(DEAD)}$ depends on IDRIVE setting			240		ns	
$t_{(DEAD)}$	Output dead time (DRV8703D-Q1)	TDEAD = 2'b00; Observed $t_{(DEAD)}$ depends on IDRIVE setting			120	ns		
		TDEAD = 2'b01; Observed $t_{(DEAD)}$ depends on IDRIVE setting			240			
		TDEAD = 2'b10; Observed $t_{(DEAD)}$ depends on IDRIVE setting			480			
		TDEAD = 2'b11; Observed $t_{(DEAD)}$ depends on IDRIVE setting			960			
$t_{(DRIVE)}$	Gate drive time				2.5		$\mu$ s	
<b>CURRENT SHUNT AMPLIFIER AND PWM CURRENT CONTROL (SP, SN, SO, VREF)</b>								
$t_s$	Settling time to $\pm 1\%$ <sup>(1)</sup>	$V_{SP} = V_{SN} = GND$ to $V_{SP} = 240$ mV, $V_{SN} = GND$ , $A_V = 10$ ; $C_{(SO)} = 200$ pF			0.5	$\mu$ s		
		$V_{SP} = V_{SN} = GND$ to $V_{SP} = 120$ mV, $V_{SN} = GND$ , $A_V = 20$ ; $C_{(SO)} = 200$ pF			1			
		$V_{SP} = V_{SN} = GND$ to $V_{SP} = 60$ mV, $V_{SN} = GND$ , $A_V = 40$ ; $C_{(SO)} = 200$ pF			2			
		$V_{SP} = V_{SN} = GND$ to $V_{SP} = 30$ mV, $V_{SN} = GND$ , $A_V = 80$ ; $C_{(SO)} = 200$ pF			4			
$t_{off}$	PWM off-time (DRV8702D-Q1)				25		$\mu$ s	
$t_{off}$	PWM off-time (DRV8703D-Q1)	TOFF = 00			25	$\mu$ s		
		TOFF = 01			50			
		TOFF = 10			100			
		TOFF = 11			200			
$t_{(BLANK)}$	PWM blanking time				2		$\mu$ s	

(1) Ensured by design

## Switching Characteristics (continued)

Over recommended operating conditions unless otherwise noted

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
<b>PROTECTION CIRCUITS</b>						
$t_{(UVLO)}$	VM UVLO falling deglitch time	VM falling; UVLO report		10	$\mu\text{s}$	
$t_{(OCP)}$	Overcurrent deglitch time	3.7	4	4.3	$\mu\text{s}$	
$t_{(RETRY)}$	Overcurrent retry time	2.8	3	3.2	ms	
$t_{(WD)}$	Watchdog time out (DRV8703D-Q1)	WD_DLY = 2'b00		10	ms	
		WD_DLY = 2'b01		20		
		WD_DLY = 2'b10		50		
		WD_DLY = 2'b11		100		
$t_{(RESET)}$	Watchdog timer reset period			64	$\mu\text{s}$	
<b>SPI</b>						
$t_{(SPI\_READY)}$	SPI read after power on	VM > VUVLO1		5	10	ms
$t_{d(SDO)}$	SDO output data delay time, CLK high to SDO high to SDO valid	$C_L = 20 \text{ pF}$		30		ns
$t_a$	SCS access time, SCS low to SDO out of high impedance			10	ns	
$t_{dis}$	SCS disable time, SCS high to SDO high impedance			10	ns	


**图 1. SPI Slave Mode Timing Definition**

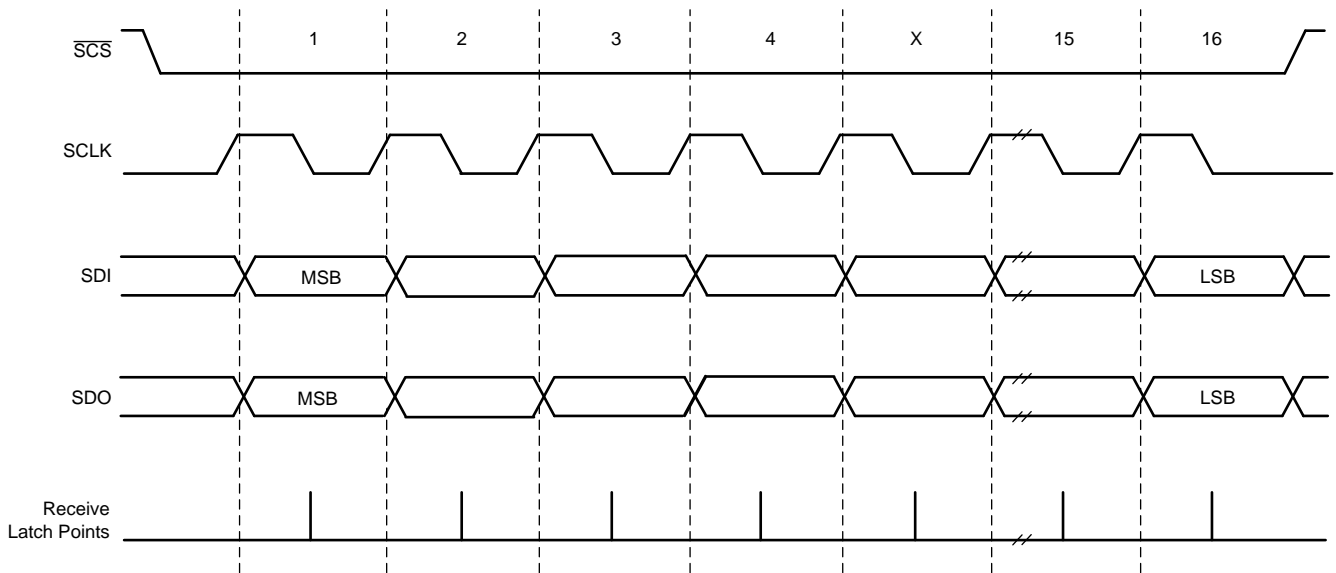


图 2. SPI Slave Mode Timing Diagram

## 6.8 Typical Characteristics

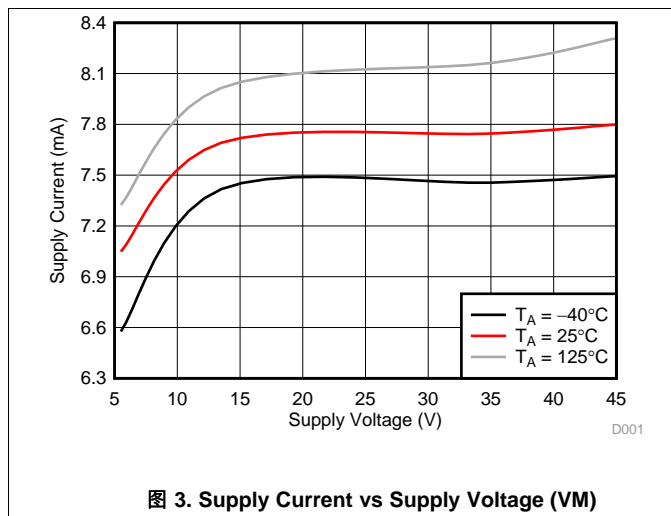


图 3. Supply Current vs Supply Voltage (VM)

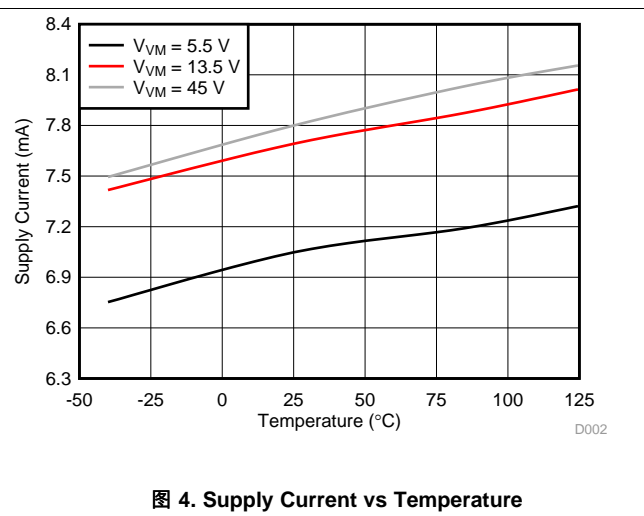


图 4. Supply Current vs Temperature

Typical Characteristics (接下页)

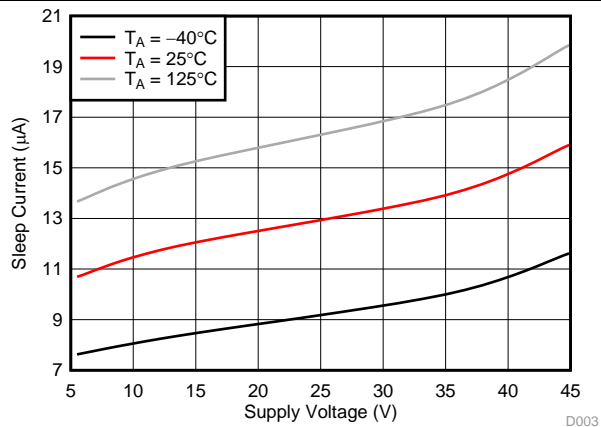


图 5. Sleep Current vs Supply Voltage (VM)

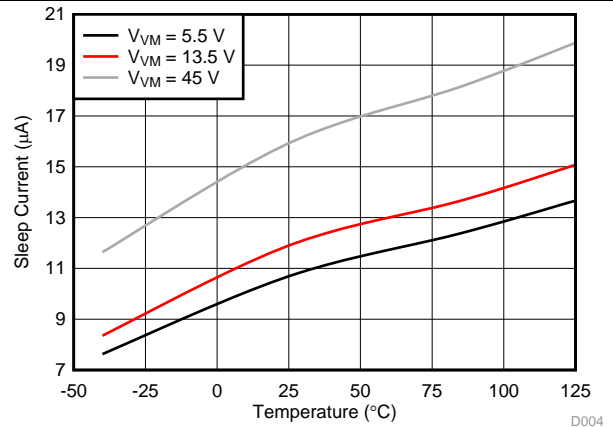


图 6. Sleep Current vs Temperature

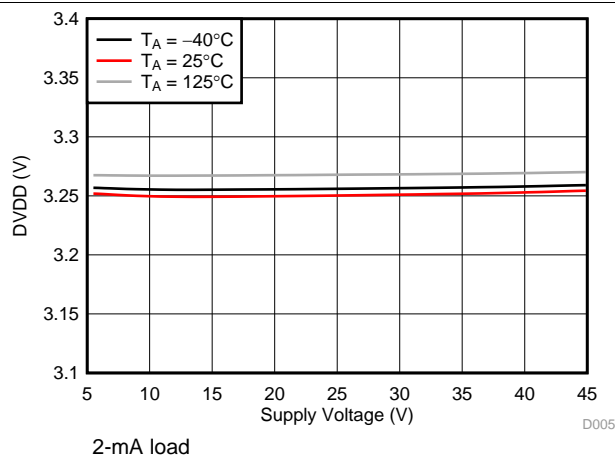


图 7. DVDD Regulator

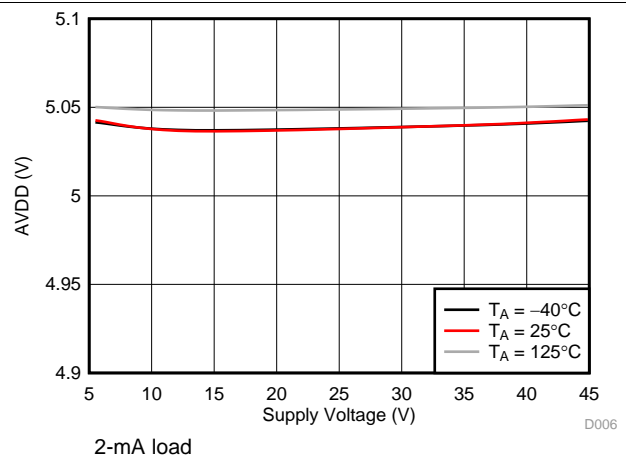


图 8. AVDD Regulator

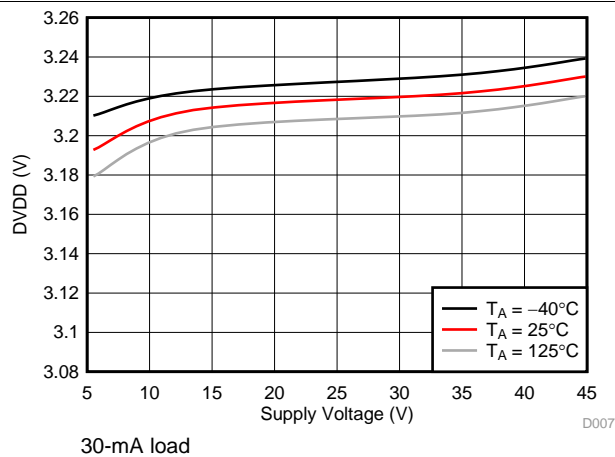


图 9. DVDD Regulator

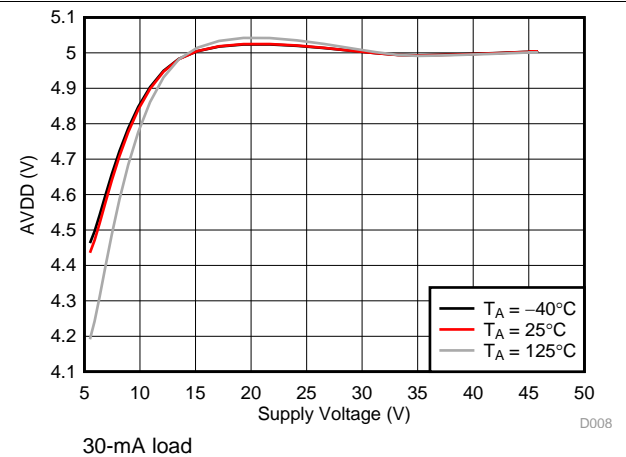


图 10. AVDD Regulator

Typical Characteristics (接下页)

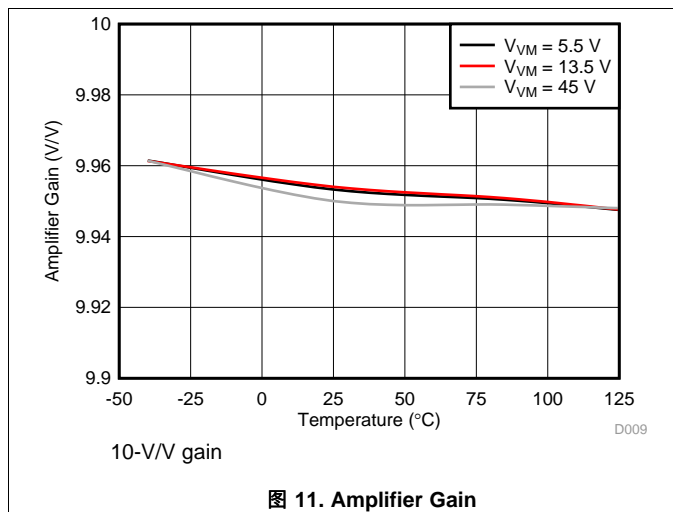


图 11. Amplifier Gain

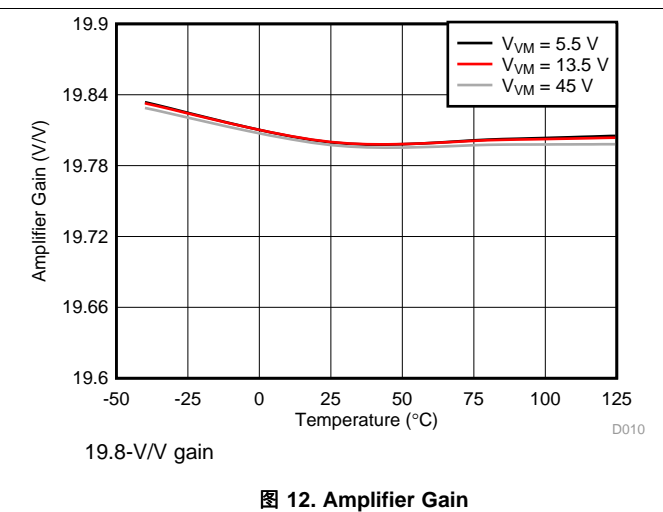


图 12. Amplifier Gain

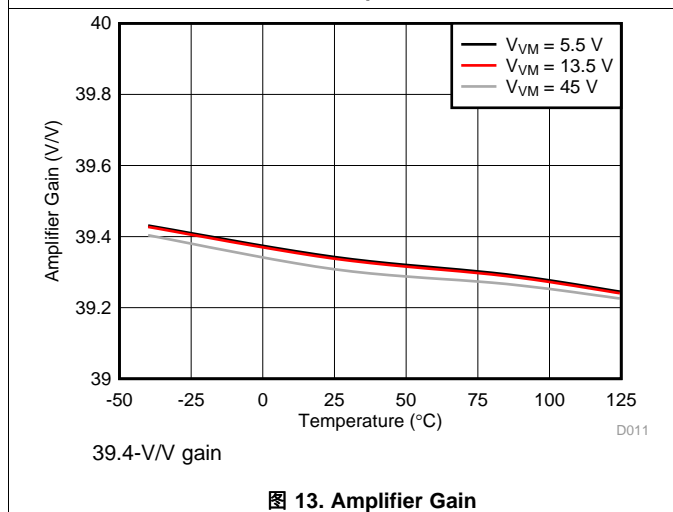


图 13. Amplifier Gain

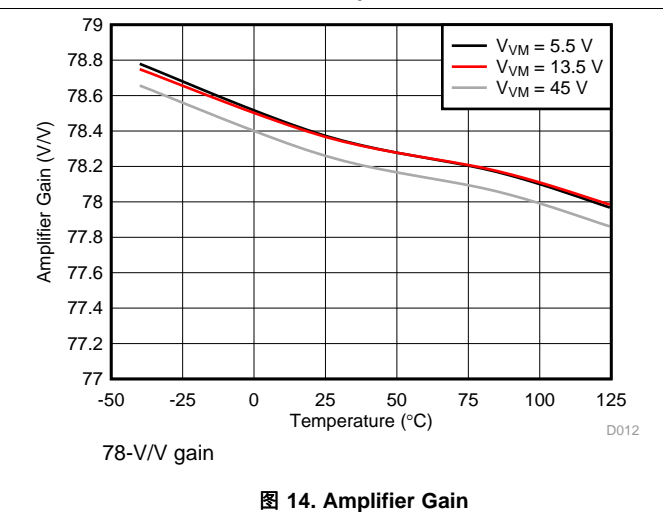


图 14. Amplifier Gain

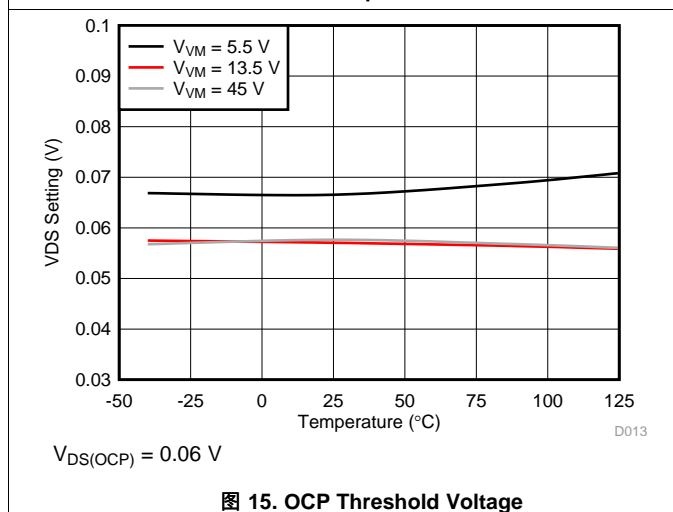


图 15. OCP Threshold Voltage

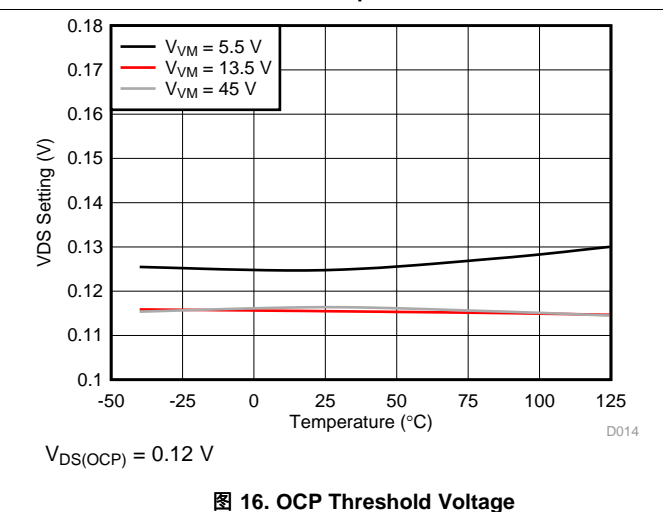


图 16. OCP Threshold Voltage

Typical Characteristics (接下页)

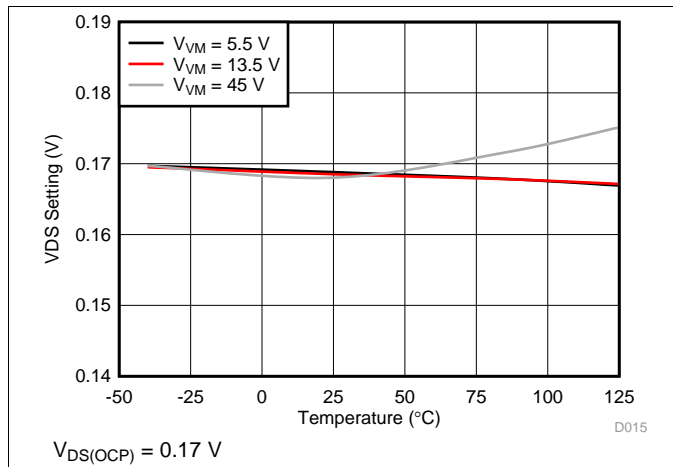


图 17. OCP Threshold Voltage

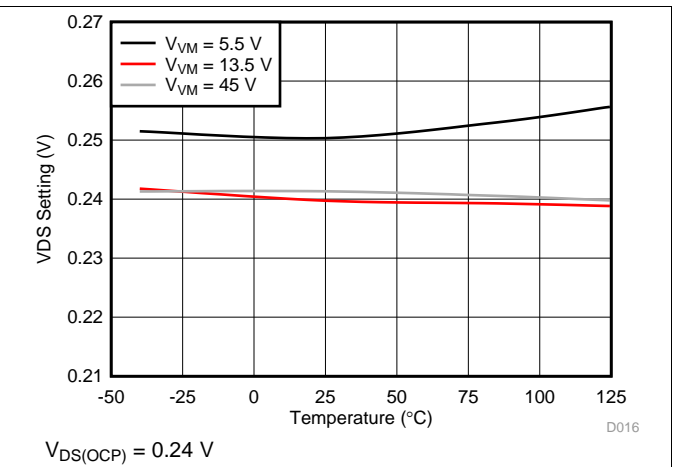


图 18. OCP Threshold Voltage

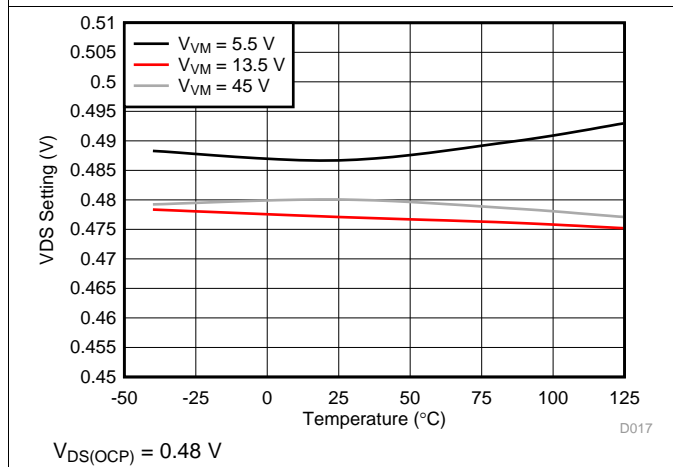


图 19. OCP Threshold Voltage

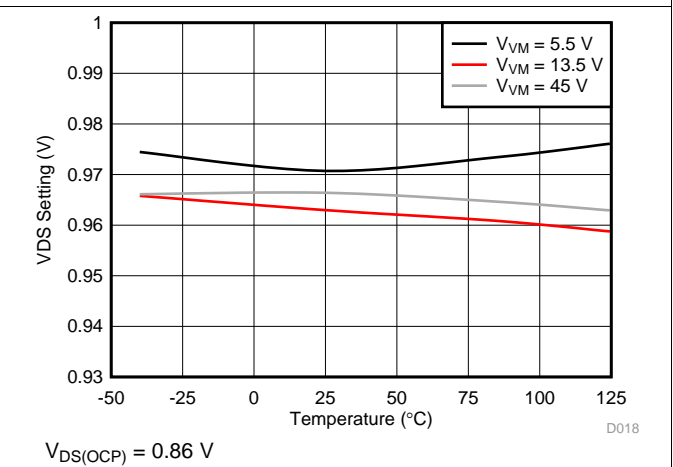


图 20. OCP Threshold Voltage

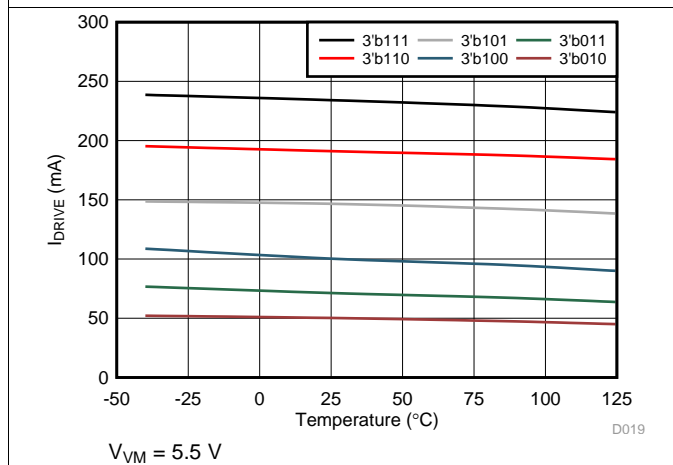


图 21. High-Side Source Current

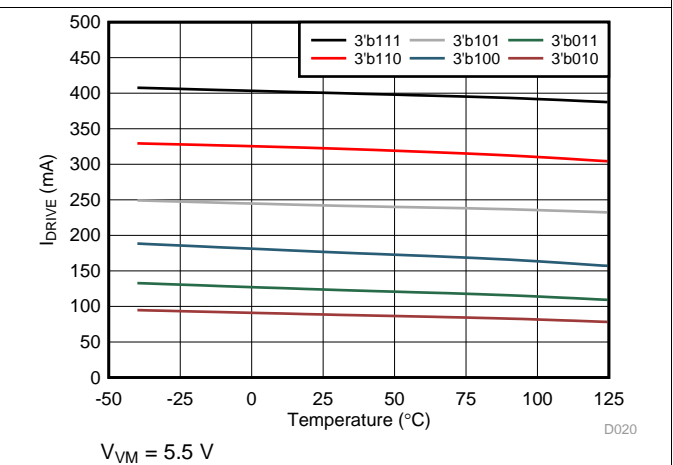


图 22. High-Side Sink Current



Typical Characteristics (接下页)

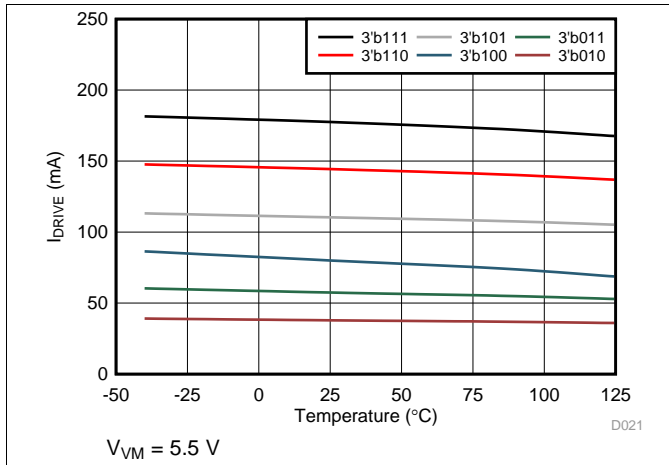


图 23. Low-Side Source Current

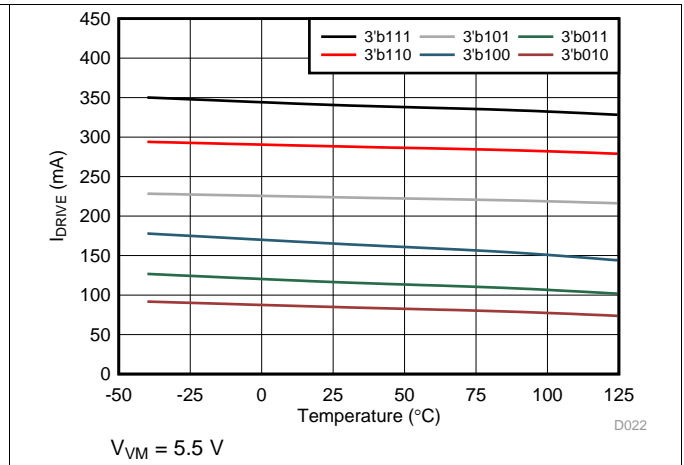


图 24. Low-Side Sink Current

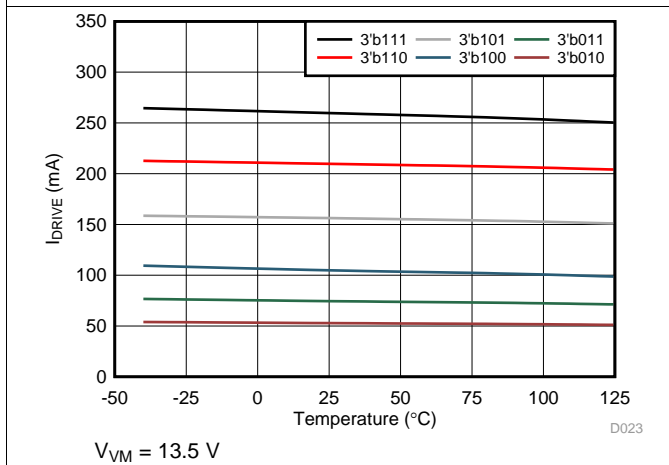


图 25. High-Side Source Current

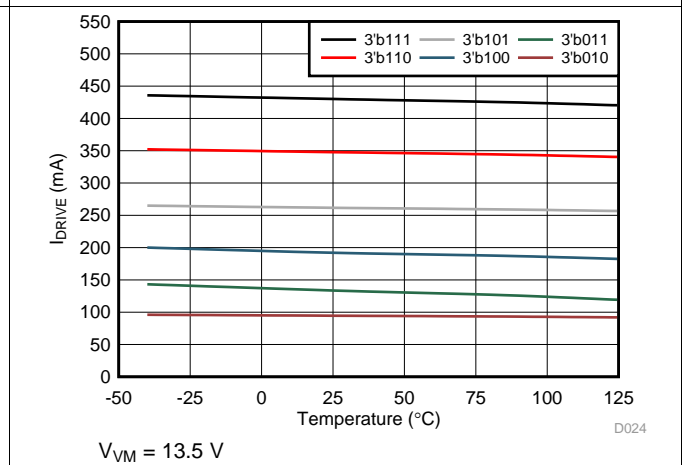


图 26. High-Side Sink Current

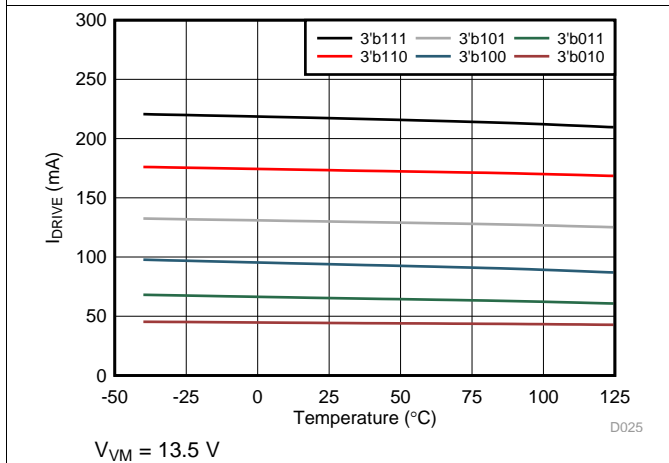


图 27. Low-Side Source Current

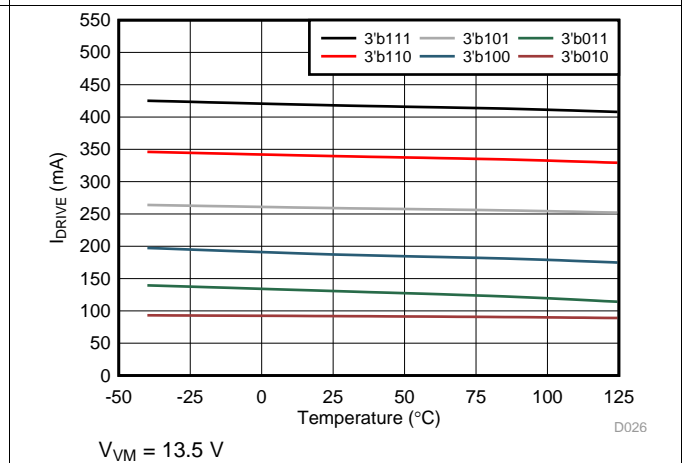


图 28. Low-Side Sink Current

## 7 Detailed Description

### 7.1 Overview

The DRV870xD-Q1 device is an half-bridge gate driver (also called a gate controller). The device integrates FET gate drivers to control two external NMOS FETs. The device can be powered with a supply voltage from 5.5 V to 45 V.

The device has a low-power sleep mode that is enabled using the nSLEEP pin.

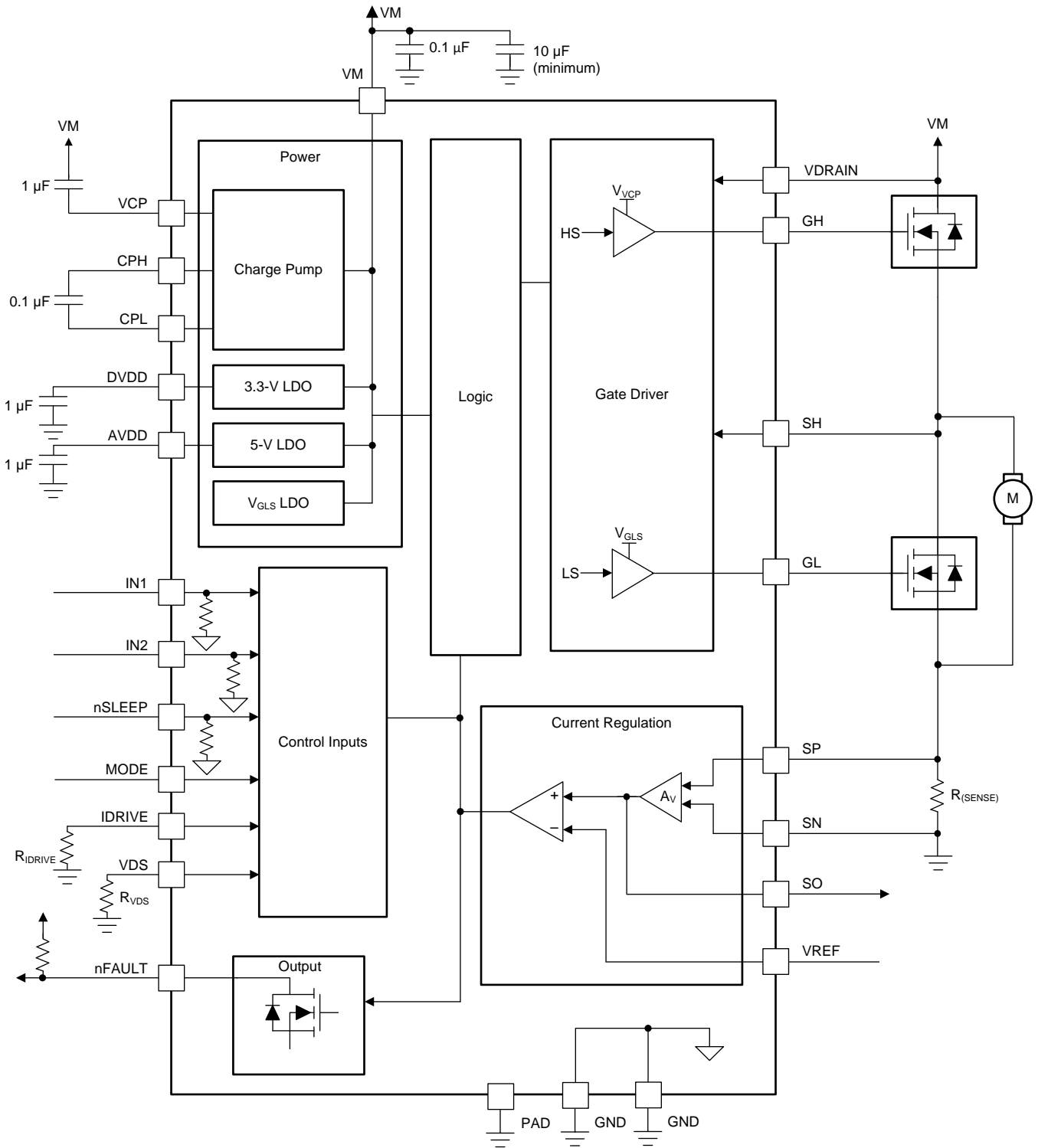
The gate drive strength can be adjusted to optimize a system for a given FET size without adding external series resistors. The IDRIVE pin allows for selection of the peak current driven into the external FET gate. Both the high-side and low-side FETs are driven with a gate source voltage ( $V_{GS}$ ) of 10.5 V (nominal) when the VM voltage is more than 13.5 V. At lower VM voltages, the  $V_{GS}$  is reduced. The high-side gate drive voltage is generated using a doubler-architecture charge pump that regulates to the  $VM + 10.5$  V.

This device significantly reduces the component count of discrete motor-driver systems by integrating the required FET drive circuitry into a single device. The DRV870xD-Q1 device also has protection features beyond traditional discrete implementations including: undervoltage lockout (UVLO), overcurrent protection (OCP), gate-driver faults, and thermal shutdown (TSD).

A start-up (inrush) or running current limitation is built in using a fixed time-off current chopping scheme. The chopping current level is set by selecting the value of the sense resistor and setting a voltage on the VREF pin.

A shunt-amplifier output provides accurate current measurements by the system controller. The SO pin outputs a voltage that is approximately 20 times the voltage across the sense resistor on the DRV8702D-Q1 device. For the DRV8703D-Q1, this gain is configurable.

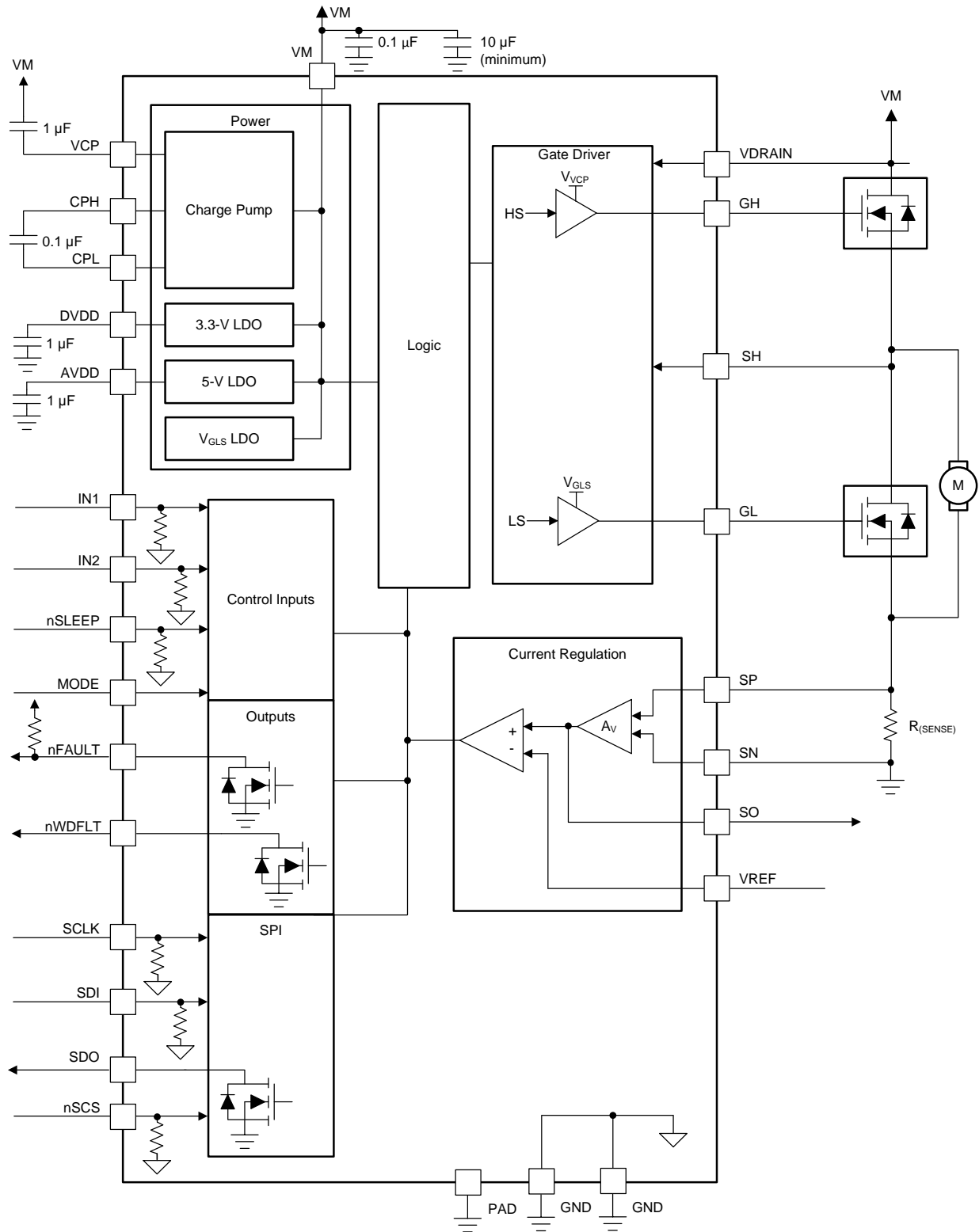
## 7.2 Functional Block Diagram



Copyright © 2017, Texas Instruments Incorporated

图 29. DRV8702D-Q1 Functional Block Diagram

Functional Block Diagram (接下页)



Copyright © 2017, Texas Instruments Incorporated

图 30. DRV8703D-Q1 Functional Block Diagram

### 7.3 Feature Description

表 1 和 表 2 列出推荐的器件外部元件。

**表 1. External Components**

COMPONENT	PIN 1	PIN 2	RECOMMENDED
$C_{(VM1)}$	VM	GND	0.1- $\mu$ F ceramic capacitor rated for VM
$C_{(VM2)}$	VM	GND	$\geq 10$ - $\mu$ F electrolytic capacitor rated for VM
$C_{(VCP)}$	VCP	VM	16-V, 1- $\mu$ F ceramic capacitor
$C_{(SW)}$	CPH	CPL	0.1- $\mu$ F X7R capacitor rated for VM
$C_{(DVDD)}$	DVDD	GND	6.3-V, 1- $\mu$ F ceramic capacitor
$C_{(AVDD)}$	AVDD	GND	6.3-V, 1- $\mu$ F ceramic capacitor
$R_{(IDRIVE)}$	IDRIVE	GND	For resistor sizing, see the <a href="#">Typical Application</a> section
$R_{(VDS)}$	VDS	GND	For resistor sizing, see the <a href="#">Typical Application</a> section
$R_{(nFAULT)}$	$V_{CC}^{(1)}$	nFAULT	$\geq 10$ k $\Omega$
$R_{(nWDFLT)}$	$V_{CC}^{(1)}$	nWDFLT	$\geq 10$ k $\Omega$
$R_{(SENSE)}$	SP	SN or GND	Optional low-side sense resistor
$R_{(VDRAIN)}^{(2)}$	VDRAIN	VM	100- $\Omega$ series resistor

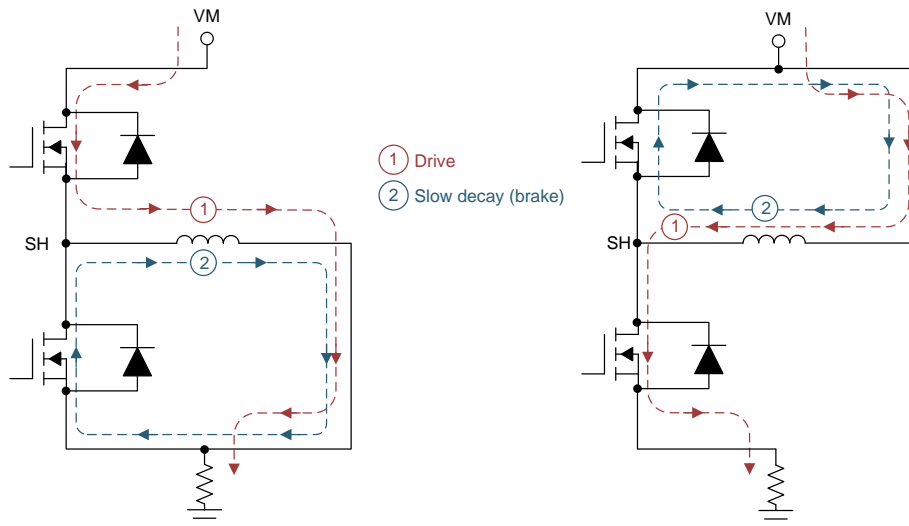
- (1) The  $V_{CC}$  pin is not a pin on the DRV870xD-Q1, but a  $V_{CC}$  supply voltage pullup is required for open-drain outputs nFAULT. These pins can be pulled up to either AVDD or DVDD.
- (2) The  $R_{(VDRAIN)}$  resistor should be used between the VDRAIN and VM pins to minimize current to the VDRAIN pin if no external reserve battery protection is implemented on the VDRAIN pin.

**表 2. External Gates**

COMPONENT	GATE	DRAIN	SOURCE	RECOMMENDED
$Q_{(HS)}$	GH	VM	SH	Supports FETs up to 200 nC at 40 kHz PWM
$Q_{(LS)}$	GL	SH	SP or GND	For more information, see <a href="#">Application and Implementation</a>

### 7.3.1 Bridge Control

The DRV870xD-Q1 device is controlled using a configurable input interface. The [Logic Tables](#) section provides the half-bridge operation states. These tables do not consider the current control built into the DRV870xD-Q1 device. The logic operation set by the MODE pin is latched on power-up or when exiting sleep mode. [图 31](#) shows the direction of the flow of current through the load when it is connected between the SH pin and GND, and between the SH pin and VM.



**图 31. Bridge Control**

#### 7.3.1.1 Logic Tables

Table 3, and Table 4 are the device logic tables. An X denotes a don't care input or output.

**注**

Any other input logic combinations, aside from the ones mentioned in [表 3](#) 和 [表 4](#), result in an error, and the device will trigger a fault.

**表 3. DRV870xD-Q1 PWM Control Interface Without Current Regulation (MODE = 1)**

nSLEEP	IN1	IN2	GH	GL	SH	AVDD/DVDD	Description
0	X	X	X	X	Hi-Z	Disabled	Sleep mode ½-bridge disabled
1	0	0	0	1	L	Enabled	½-bridge low side on
1	1	0	1	0	H	Enabled	½-bridge high side on

**表 4. DRV870xD-Q1 PWM Control Interface With Current Regulation (MODE = Hi-Z)**

nSLEEP	IN1	IN2	GH	GL	SH	AVDD/DVDD	Description
0	X	X	X	X	Hi-Z	Disabled	Sleep mode ½-bridge disabled
1	0	0	0	0	Hi-Z	Enabled	½-bridge is in tri-state
1	1	0	1	0	H	Enabled	½-bridge high-side on
1	1	1	0	1	L	Enabled	½-bridge low-side on

If MODE = Hi-Z is selected, the device performs current regulation (refer to the [Current Regulation](#) section). Having both the input (INx) pins high puts the motor in brake mode (low-side slow decay). If MODE = 1 is selected, current regulation is disabled and must be performed externally using a MCU. With MODE = 1, the load current recirculation occurs through the high-side FET as shown in [图 31](#).

### 7.3.2 MODE Pin

The MODE pin of the device determines the control interface and latches on power-up or when exiting sleep mode. 图 32 shows an overview of the internal circuit of the MODE pin.

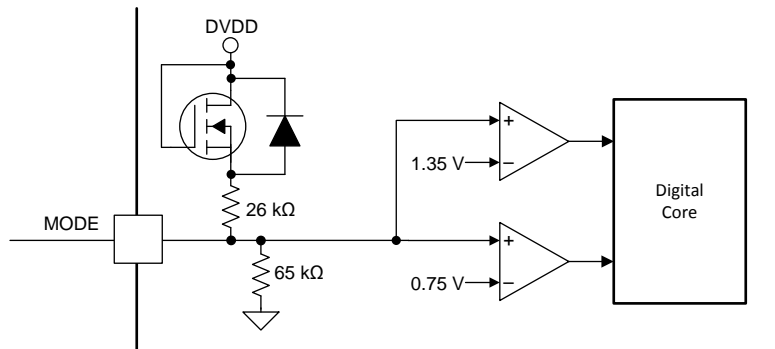


图 32. MODE Pin Block Diagram

表 5 lists the different control interfaces that can be set via MODE pin at power-up or when exiting sleep mode.

表 5. MODE Pin Configuration

MODE	CONTROL INTERFACE
1	PWM control interface without current regulation
Hi-Z	PWM control interface with current regulation

During the device power-up sequence, the DVDD pin is enabled first. Then the MODE pin latches. Finally the AVDD pin is enabled. For setting PWM control interface, TI does not recommend connecting the MODE pin to the AVDD pin. Instead the MODE pin should be connected to an external 5-V or 3.3-V supply or to the DVDD pin if not driven by an external microcontroller (MCU).

### 7.3.3 nFAULT Pin

The nFAULT pin has an open-drain output and should be pulled up to a 5-V or 3.3-V supply. When a fault is detected, the nFAULT line is logic low.

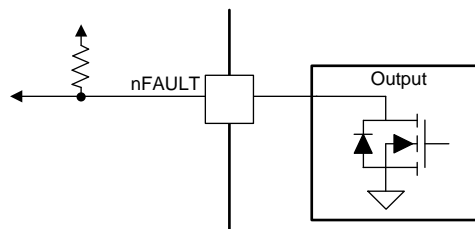


图 33. nFAULT Block Diagram

For a 3.3-V pullup the nFAULT pin can be tied to the DVDD pin with a resistor (refer to the [Application and Implementation](#) section). For a 5-V pullup an external 5-V supply should be used. TI does not recommend connecting the nFAULT pin to the AVDD pin.

### 7.3.4 Current Regulation

The maximum current through the motor winding is regulated by a fixed off-time PWM current regulation or current chopping. When an half-bridge is enabled, current rises through the winding at a rate dependent on the DC voltage and inductance of the winding. When the current hits the current chopping threshold, the bridge enters a brake (low-side slow decay) mode until the  $t_{off}$  time expires.

## 注

Immediately after the current is enabled, the voltage on the SP pin is ignored for a period ( $t_{\text{BLANK}}$ ) before enabling the current-sense circuitry.

The PWM chopping current is set by a comparator that compares the voltage across a current-sense resistor connected to the SP pin, multiplied by a factor of  $A_V$ , with a reference voltage from the VREF pin. The factor  $A_V$  is the shunt-amplifier gain, which is 19.8 V/V for the DRV8702D-Q1 device or configurable to 10, 19.8, 39.4, or 78 V/V for the DRV8703D-Q1 device.

Use [公式 1](#) to calculate the chopping current ( $I_{\text{CHOP}}$ ).

$$I_{\text{(CHOP)}} = \frac{V_{\text{VREF}} - V_{\text{IO}}}{A_V \times R_{\text{(SENSE)}}} \quad (1)$$

For example, if a 50-m $\Omega$  sense resistor and a VREF value of 3.3 V are selected, the full-scale chopping current is 3.28 A. The  $A_V$  is 19.8 V/V and  $V_{\text{IO}}$  is assumed to be 50 mV in this example.

## 注

If the load is connected between the SH pin and VM and current regulation is enabled (MODE pin is Hi-Z), the low-side FET is switched on when the current flowing through the load exceeds the ICHOP threshold. This result in an adverse effect by driving the load at 100% duty cycle because the maximum current flows through the load as the low-side FET remains switched on for the  $t_{\text{OFF}}$  duration. Texas Instruments recommends using the PWM control interface without current regulation (MODE pin is 1) for this configuration to drive the load.

For DC motors, current regulation is used to limit the start-up and stall current of the motor. If the current regulation feature is not needed, it can be disabled by tying the VREF pin directly to the AVDD pin. If the PWM control-interface mode without current regulation (MODE pin is 1) is selected for operation, the device does not perform PWM current regulation or current chopping.

### 7.3.5 Amplifier Output (SO)

The SO pin on the DRV870xD-Q1 device outputs an analog voltage equal to the voltage across the SP and SN pins multiplied by  $A_V$ . The SO voltage is only valid for when the load is connected in the way shown in [图 31](#). Use [公式 2](#) to calculate the approximate current for the half-bridge.

$$I = \frac{V_{\text{SO}} - V_{\text{IO}}}{A_V \times R_{\text{(SENSE)}}} \quad (2)$$

When the SP and SN voltages are 0 V, the SO pin outputs the amplifier offset voltage,  $V_{\text{IO}}$ . No capacitor is required on the SO pin.



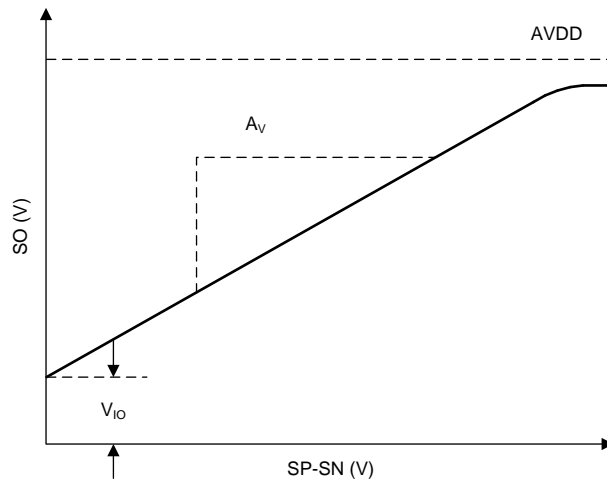


图 34. Current Sense Amplifier Output

If the voltage across the SP and SN pins exceeds 1 V, then the DRV870xD-Q1 device flags an overcurrent condition.

The SO pin can source up to 5 mA of current. If the pin is shorted to ground, or if this pin drives a higher current load, the output functions as a constant-current source. The output voltage is not representative of the half-bridge current in this state.

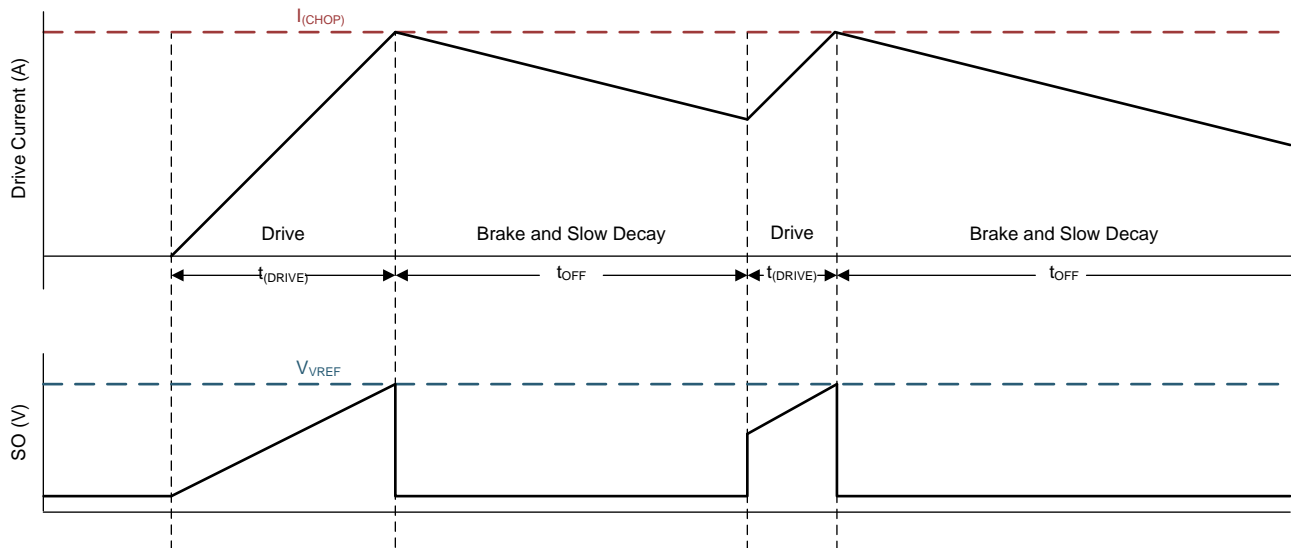


图 35. Current Sense Amplifier and Current Chopping Operation

During brake mode (slow decay), current is circulated through the low-side FET. Because current is not flowing through the sense resistor, the SO pin does not represent the motor current.

### 7.3.5.1 SO Sample and Hold Operation

The DRV8703D-Q1 device allows the shunt amplifier to operate in a sample and hold configuration. To enable this mode, set the SH\_EN bit high through the SPI. In this mode, the shunt amplifier output is disabled to the Hi-Z state whenever the driver is in a brake mode. Place an external capacitor on this pin.

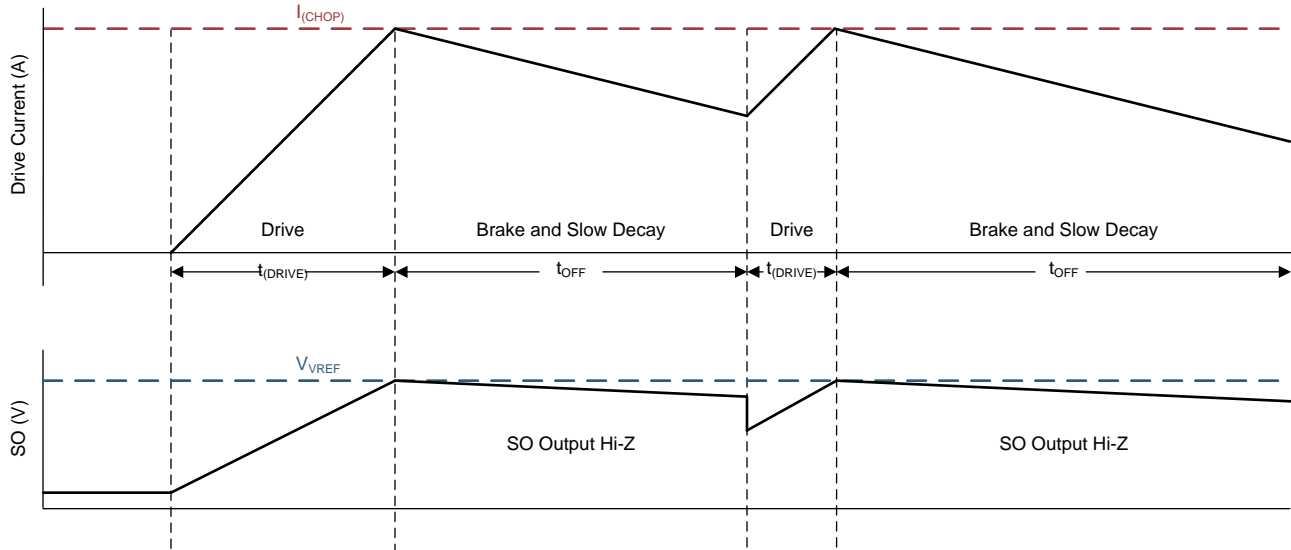


图 36. Sample and Hold Operation

### 7.3.6 PWM Motor Gate Drivers

The DRV870xD-Q1 device has gate drivers for a single half-bridge with external NMOS FETs. 图 37 shows a block diagram of the predrive circuitry.

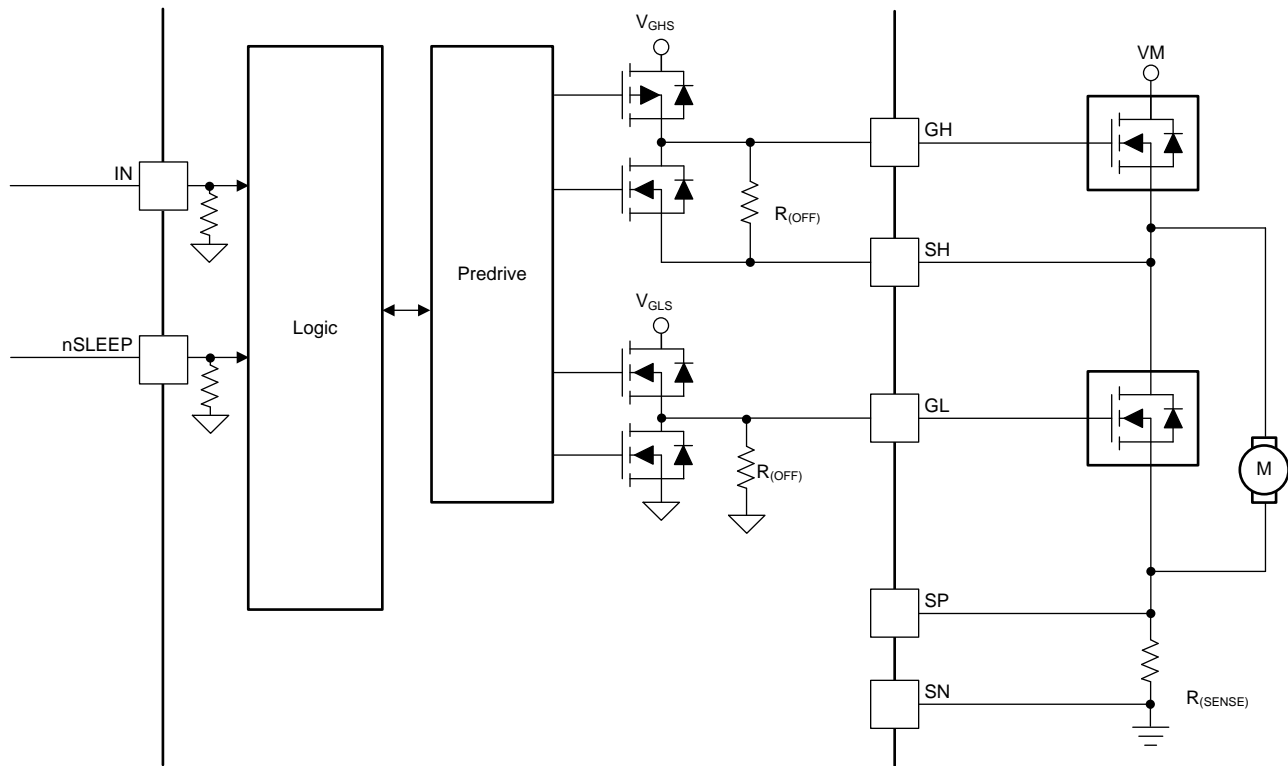


图 37. Predrive Block Diagram

Gate drivers inside the DRV870xD-Q1 device directly drive N-Channel MOSFETs, which drive the motor current. The high-side gate drive is supplied by the charge pump, while an internal regulator generates the low-side gate drive.

The peak drive current of the gate drivers is adjustable through the IDRIVE pin for DRV8702D-Q1 device or the IDRIVE register for the DRV8703D-Q1 device. Peak source currents can be set to the values listed in the FET gate drivers section of the [Electrical Characteristics](#) table. The peak sink current is approximately two times the peak source current. Adjusting the peak current changes the output slew rate, which also depends on the FET input capacitance and gate charge.

Fast switching times can cause extra noise on the VM and GND pins. This additional noise can occur specifically because of a relatively slow reverse-recovery time of the low-side body diode, when the body diode conducts reverse-bias momentarily, similar to shoot-through. Slow switching times can cause excessive power dissipation because the external FETs have a longer turnon and turnoff time.

When changing the state of the output, the peak current ( $I_{DRIVE}$ ) is applied for a short period ( $t_{(DRIVE)}$ ), to charge the gate capacitance. After this time, a weak current source ( $I_{HOLD}$ ) is used to keep the gate at the desired state. When selecting the gate drive strength for a given external FET, the selected current must be high enough to charge fully and discharge the gate during  $t_{(DRIVE)}$ , or excessive power is dissipated in the FET.

During high-side turnon, the low-side gate is pulled low with a strong pulldown ( $I_{STRONG}$ ). This pulldown prevents the low-side FET  $Q_{GS}$  from charging and keeps the FET off, even when fast switching occurs at the outputs.

The gate-driver circuits include enforcement of a dead time in analog circuitry, which prevents the high-side and low-side FETs from conducting at the same time. When the switching FETs are on, this handshaking prevents the high-side or low-side FET from turning on until the opposite FET turns off.

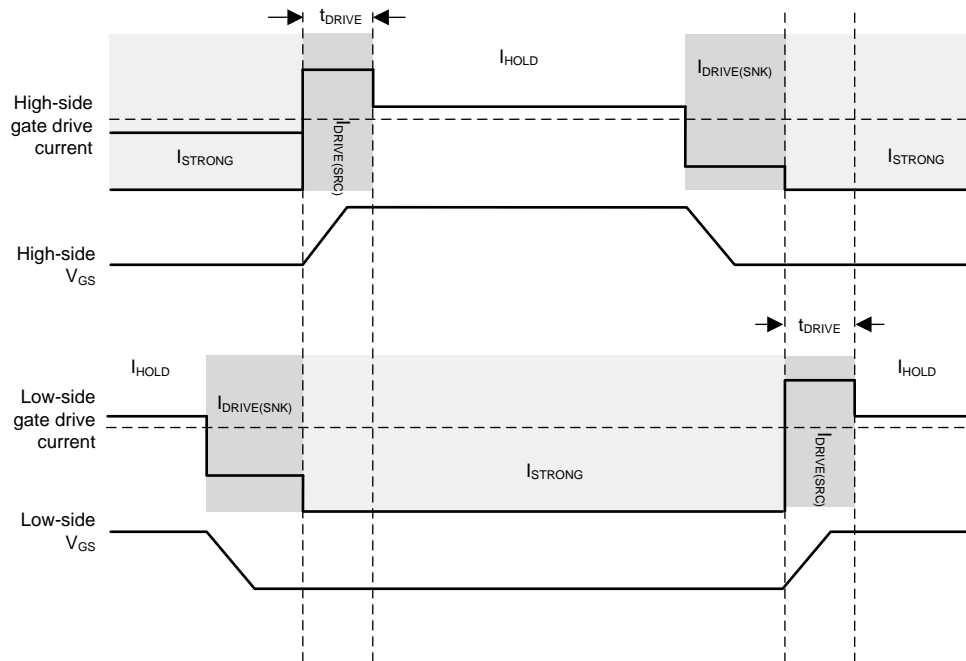


图 38. Gate Driver Output to Control External FETs

7.3.6.1 Miller Charge ( $Q_{GD}$ )

When a FET gate turns on, the following capacitances must be charged:

- Gate-to-source charge,  $Q_{GS}$
- Gate-to-drain charge,  $Q_{GD}$  (Miller charge)
- Remaining  $Q_G$

The FET output is slewing primarily during the  $Q_{GD}$  charge.

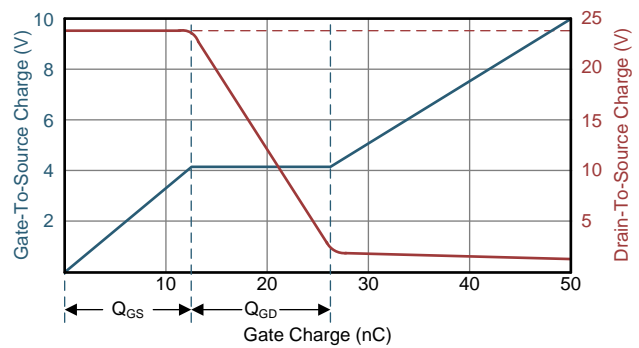
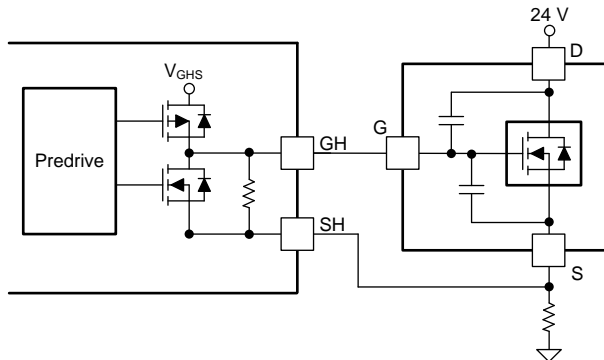


图 39. FET Gate Charging Profile

### 7.3.7 IDRIVE Pin (DRV8702D-Q1 Only)

The rise and fall times of the half-bridge output (SH pin) can be adjusted by setting the IDRIVE resistor value or forcing a voltage onto the IDRIVE pin. The FET gate voltage ramps faster if a higher IDRIVE setting is selected. The ramp of the FET gate directly affects the rise and fall times of the half-bridge output.

Tying the IDRIVE pin to ground selects the lowest drive setting of 10-mA source and 20-mA sink. Leaving this pin open selects the drive setting of 155-mA high side and 130-mA low side for source current, and 265-mA high side, 260-mA low side for sink current, at a VM voltage of 13.5 V. For a detailed list of IDRIVE configurations, see 表 6.

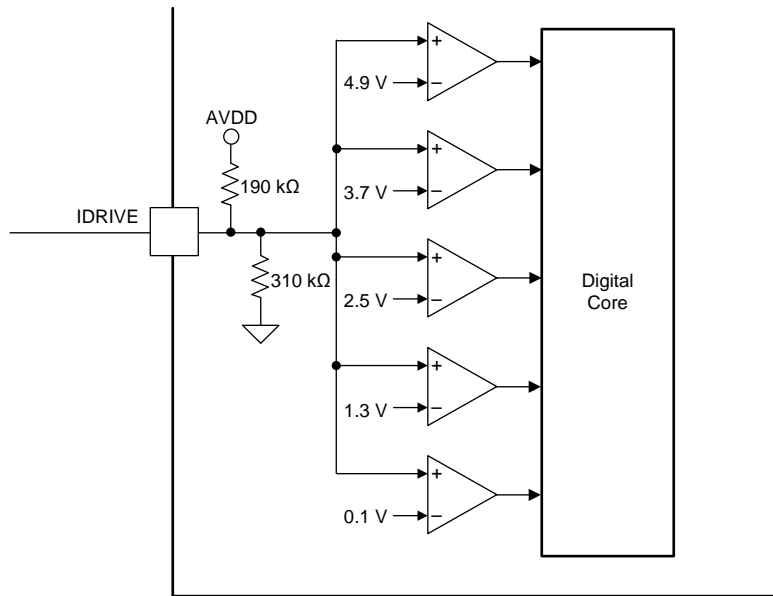
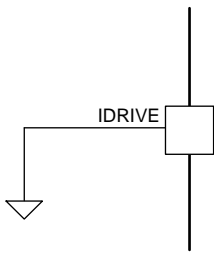
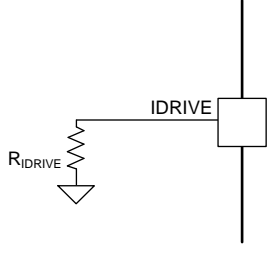
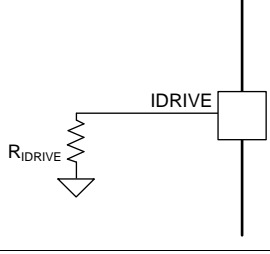
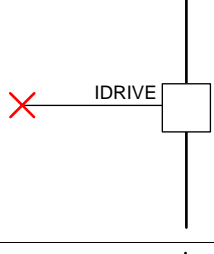
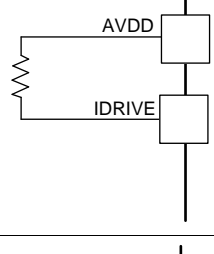
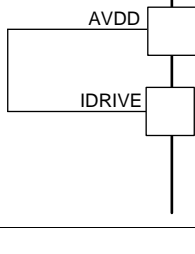


图 40. IDRIVE Pin Internal Circuitry

表 6. DRV8702D-Q1 IDRIVE Settings

IDRIVE RESISTANCE	IDRIVE VOLTAGE	SOURCE CURRENT		SINK CURRENT		CIRCUIT
		V <sub>VM</sub> = 5.5 V	V <sub>VM</sub> = 13.5 V	V <sub>VM</sub> = 5.5 V	V <sub>VM</sub> = 13.5 V	
< 1 kΩ to GND	GND	High-side: 10 mA Low-side: 10 mA	High-side: 10 mA Low-side: 10 mA	High-side: 20 mA Low-side: 20 mA	High-side: 20 mA Low-side: 20 mA	
33 kΩ ± 5% to GND	0.7 V ± 5%	High-side: 20 mA Low-side: 20 mA	High-side: 20 mA Low-side: 20 mA	High-side: 40 mA Low-side: 40 mA	High-side: 40 mA Low-side: 40 mA	
200 kΩ ± 5% to GND	2 V ± 5%	High-side: 50 mA Low-side: 40 mA	High-side: 50 mA Low-side: 45 mA	High-side: 90 mA Low-side: 85 mA	High-side: 95 mA Low-side: 95 mA	
> 2 MΩ to GND, Hi-Z	3 V ± 5%	High-side: 145 mA Low-side: 115 mA	High-side: 155 mA Low-side: 130 mA	High-side: 250 mA Low-side: 235 mA	High-side: 265 mA Low-side: 260 mA	
68 kΩ ± 5% to AVDD	4 V ± 5%	High-side: 190 mA Low-side: 145 mA	High-side: 210 mA Low-side: 180 mA	High-side: 330 mA Low-side: 300 mA	High-side: 350 mA Low-side: 350 mA	
< 1 kΩ to AVDD	AVDD	High-side: 240 mA Low-side: 190 mA	High-side: 260 mA Low-side: 225 mA	High-side: 420 mA Low-side: 360 mA	High-side: 440 mA Low-side: 430 mA	

### 7.3.8 Dead Time

The dead time ( $t_{DEAD}$ ) is measured as the time when the SH pin is in the Hi-Z state between turning off one of the half-bridge FETs and turning on the other. For example, the output is Hi-Z between turning off the high-side FET and turning on the low-side FET.

The dead time consists of an inserted digital dead time and FET gate slewing. The DRV8702D-Q1 device has a digital dead time of approximately 240 ns. The DRV8703D-Q1 device has programmable dead-time options of 120, 240, 480, 960 ns. In addition to this digital dead time, the output is Hi-Z as long as the voltage across the GL pin to ground or GH pin to SH pin is less than the FET threshold voltage.

The total dead time is dependent on the IDRIVE resistor setting because a portion of the FET gate ramp (GH and GL pins) includes the observable dead time.

### 7.3.9 Propagation Delay

The propagation delay time ( $t_{PD}$ ) is measured as the time between an input edge to an output change. This time is composed of two parts: an input deglitcher and output slewing delay. The input deglitcher prevents noise on the input pins from affecting the output state.

The gate drive slew rate also contributes to the delay time. For the output to change state during normal operation, one FET must first be turned off. The FET gate is ramped down according to the IDRIVE resistor selection, and the observed propagation delay ends when the FET gate falls below the threshold voltage.

### 7.3.10 Overcurrent VDS Monitor

The gate-driver circuit monitors the VDS voltage of each external FET when it is driving current. When the voltage monitored is greater than the OCP threshold voltage ( $V_{DS(OCP)}$ ) after the OCP deglitch time has expired, an OCP condition is detected. The VDS voltage can be adjusted by changing the resistor ( $R_{(VDS)}$ ) on the VDS pin of the DRV8702D-Q1 device. The DRV8703D-Q1 device provides VDS voltage levels by setting the VDS register.

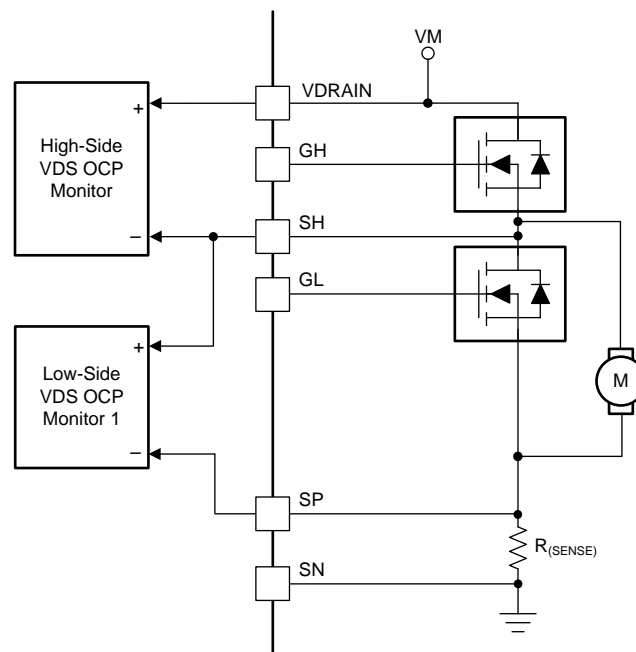


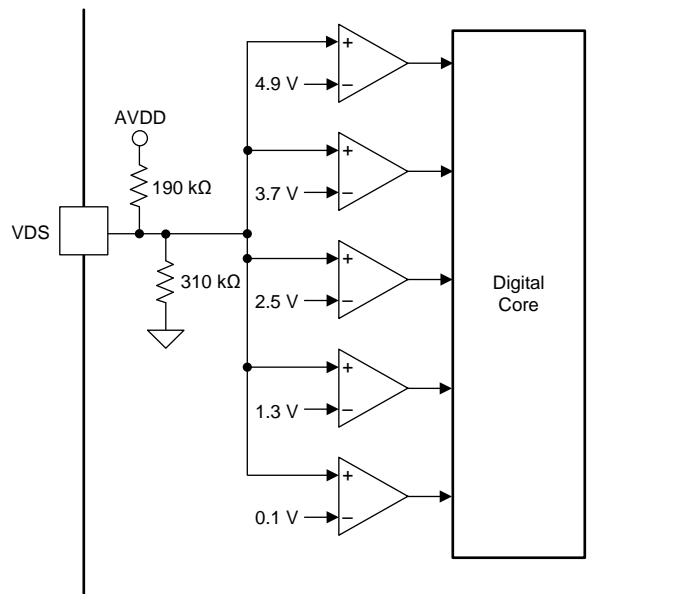
图 41.  $V_{DS(OCP)}$  Block Diagram

The VDS voltage on the high-side FET is measured across the VDRAIN to SH pin. The low-side VDS monitor measures the VDS voltage across the SH to SP pins. Ensure that the SP pin is always connected to the source of the low-side FET of half-bridge, even when the sense amplifier is not used.

### 7.3.11 VDS Pin (DRV8702D-Q1 Only)

The VDS pin on the DRV8702D-Q1 device is used to select the VDS threshold voltage for overcurrent detection.

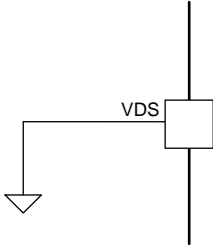
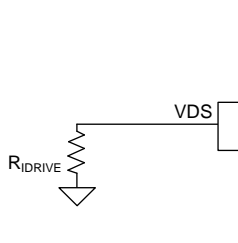
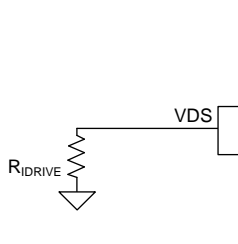
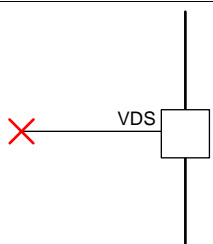
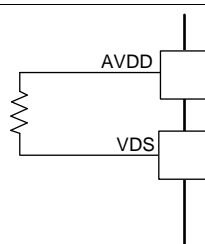
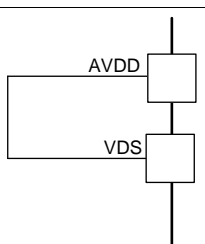
Tying the VDS pin to ground selects the lowest setting of 0.06 V. Leaving this pin open selects the setting of 0.48 V. Tying the VDS pin to the AVDD the pin disables the VDS monitor. For a detailed list of VDS configurations, see [表 7](#).



**图 42. VDS Block Diagram**



表 7. VDS Pin Resistor Setting

VDS RESISTANCE	VDS VOLTAGE	OVERCURRENT TRIP LEVEL ( $V_{DS(OCF)}$ )	CIRCUIT
< 1 k $\Omega$ to GND	GND	0.06 V	
33 k $\Omega$ $\pm$ 5% to GND	0.7 V $\pm$ 5%	0.12 V	
200 k $\Omega$ $\pm$ 5% to GND	2 V $\pm$ 5%	0.24 V	
> 2 M $\Omega$ to GND, Hi-Z	3 V $\pm$ 5%	0.48 V	
68 k $\Omega$ $\pm$ 5% to AVDD	4 V $\pm$ 5%	0.96 V	
< 1 k $\Omega$ to AVDD	AVDD	Disabled	

### 7.3.12 Charge Pump

A charge pump is integrated to supply the gate drive voltage of a high-side NMOS ( $V_{GS_H}$ ). The charge pump requires a capacitor between the VM and VCP pins. Additionally, a low-ESR ceramic capacitor is required between the CPH and CPL pins. When the VM voltage is below 13.5 V, this charge pump functions as a doubler and generates a  $V_{VCP}$  equal to  $2 \times V_{VM} - 1.5$  V if unloaded. When the VM voltage is more than 13.5 V, the charge pump regulates  $V_{VCP}$  such that it is equal to  $V_{VM} + 10.5$  V.

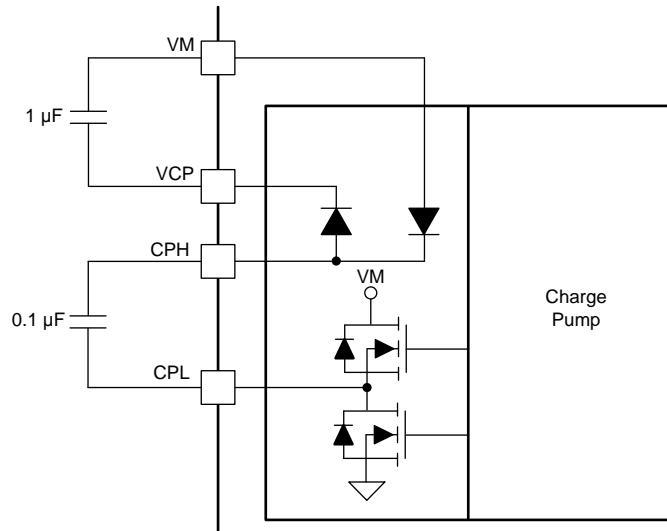


图 43. Charge Pump Block Diagram

### 7.3.13 Gate Drive Clamp

A clamping structure limits the gate-drive output voltage to the  $V_{C(GS)}$  voltage to protect the power FETs from damage. The positive voltage clamp is realized using a series of diodes. The negative voltage clamp uses the body diodes of the internal predriver FET.

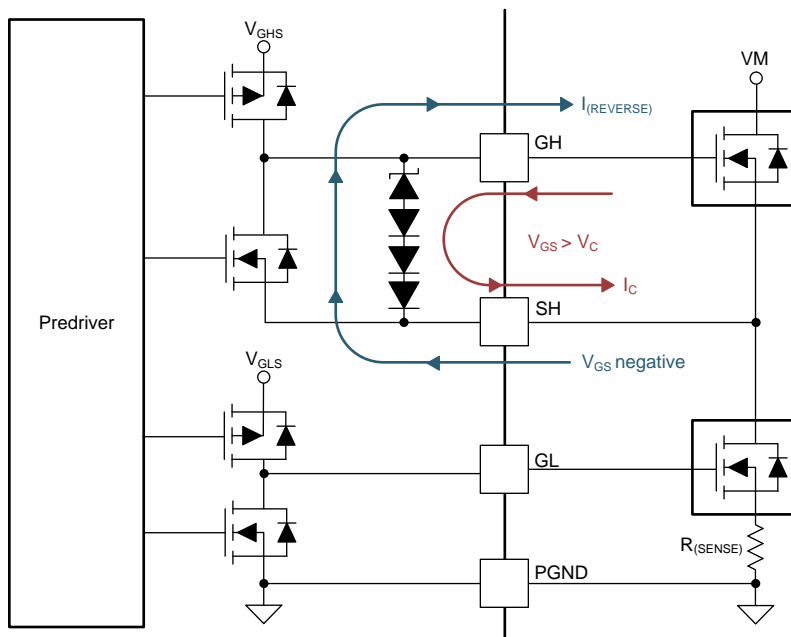


图 44. Gate Drive Clamp

### 7.3.14 Protection Circuits

The DRV870xD-Q1 device is fully protected against VM undervoltage, charge-pump undervoltage, overcurrent, gate-driver shorts, and overtemperature events.

#### 7.3.14.1 VM Undervoltage Lockout (UVLO2)

If the voltage on the VM pin falls below the VM undervoltage lockout threshold voltage ( $V_{UVLO2}$ ), both FETs in the half-bridge are disabled, the charge pump is disabled, and the nFAULT pin is driven low. The VM\_UVFL bit of the DRV8703D-Q1 device is set. The operation resumes when the VM voltage rises above the UVLO2 threshold. The nFAULT pin is released after the operation resumes but the VM\_UVFL bit on the DRV8703D-Q1 device remains set until cleared by writing to the CLR\_FLT bit.

The SPI settings on the DRV8703D-Q1 device are not reset by this fault even though the output drivers are disabled. The settings are maintained and internal logic remains active until the VM voltage falls below the logic undervoltage threshold ( $V_{UVLO1}$ ).

#### 7.3.14.2 Logic Undervoltage (UVLO1)

If the voltage on the VM pin falls below the logic undervoltage threshold voltage ( $V_{UVLO1}$ ), the internal logic is reset. The operation resumes when the VM voltage rises above the UVLO1 threshold. The nFAULT pin is logic low during this state because it is pulled low when the VM undervoltage condition occurs. Decreasing the VM voltage below this undervoltage threshold resets the SPI settings.

#### 7.3.14.3 VCP Undervoltage Lockout (CPUV)

If the voltage on the VCP pin falls below the threshold voltage of the charge-pump undervoltage (CPUV) lockout, both FETs in the half-bridge are disabled and the nFAULT pin is driven low. The DRV8703D-Q1 the VCP\_UVFL bit is set. The operation resumes when the VCP voltage rises above the CPUV threshold. The nFAULT pin is released after the operation resumes but the VCP\_UVFL bit on the DRV8703D-Q1 device remains set until cleared by writing to the CLR\_FLT bit.

#### 7.3.14.4 Overcurrent Protection (OCP)

Overcurrent is sensed by monitoring the VDS voltage drop across the external FETs. If the voltage across a driven FET exceeds the  $V_{DS(OCP)}$  level for longer than the OCP deglitch time, an OCP event is recognized. Both FETs in the half-bridge are disabled, and the nFAULT pin is driven low. The OCP bit of the DRV8703D-Q1 device is set. The drive re-enables after the  $t_{(RETRY)}$  time has passed. The nFAULT pin becomes high again after the retry time.

If the fault condition is still present, the cycle repeats. If the fault is no longer present, normal operation resumes and the nFAULT pin goes high. The OCP bit on the DRV8703D-Q1 remains set until cleared by writing to the CLR\_FLT bit. In addition to this FET VDS monitor, an overcurrent condition is detected if the voltage at the SP pin exceeds  $V_{SP(OCP)}$  and the nFAULT pin is driven low. The OCP bit in the DRV8703-Q1 device is set.

#### 7.3.14.5 Gate Driver Fault (GDF)

The GH and GL pins are monitored such that if the voltage on the external FET gate does not increase or decrease after the  $t_{(DRIVE)}$  time, a gate driver fault is detected. This fault occurs if the GH or GL pins are shorted to the GND, SH, or VM pin. Additionally, a gate-driver fault occurs if the selected IDRIVE setting is not sufficient to turn on the external FET. Both FETs in the half-bridge are disabled, and the nFAULT pin is driven low. The GDF bit of the DRV8703D-Q1 device is set. The driver re-enables after the OCP retry period ( $t_{(RETRY)}$ ) has passed. The nFAULT pin is released after the operation has resumed but the GDF bit on the DRV8703D-Q1 device remains set until cleared by writing to the CLR\_FLT bit.

#### 7.3.14.6 Thermal Shutdown (TSD)

If the die temperature exceeds the  $T_{SD}$  temperature, both FETs in the half-bridge are disabled, the charge pump shuts down, the AVDD regulator is disabled, and the nFAULT pin is driven low. The OTSD bit of the DRV8703D-Q1 device is set as well. After the die temperature falls below  $T_{SD} - T_{hys}$  temperature, device operation automatically resumes. The nFAULT pin is released after the operation resumes, but the OTSD bit on the DRV8703D-Q1 device remains set until cleared by writing to the CLR\_FLT bit.

### 7.3.14.7 Watchdog Fault (WDFLT, DRV8703D-Q1 Only)

An MCU watchdog function can be enabled to ensure that the external controller that is instructing the DRV8703D-Q1 device is active and in a known state. The SPI watchdog must be enabled by writing a 1 to the WD\_EN bit through the SPI (disabled by default, bit is 0). When the watchdog is enabled, an internal timer starts to count down to an interval set by the WD\_DLY bits. The register address 0x00 must be read by the MCU within the interval set by the WD\_DLY bit to reset the watchdog. If the timer is allowed to expire, the nWDFLT pin is enabled. When the nWDFLT pin is enabled the following occurs:

- The nWDFLT pin goes low for 64  $\mu$ s.
- The nFAULT pin is asserted.
- The WD\_EN bit is cleared.
- The drivers are disabled.

The WDFLT bit remains asserted, and operation is halted until the CLR\_FLT bit has been written to 1.

表 8 lists the fault responses of the device under the fault conditions.

**表 8. Fault Response**

FAULT	CONDITION	HALF-BRIDGE	CHARGE PUMP	AVDD	DVDD	RECOVERY
VM undervoltage (UVLO)	$V_{VM} \leq V_{(UVLOx)}$ (5.45 V, max)	Disabled	Disabled	Disabled	Operating	$V_{VM} \geq V_{(UVLOx)}$ (5.65 V, max)
VCP undervoltage (CPUV)	$V_{VCP} \leq V_{(CP\_UV)}$ ( $V_{VM} + 1.5$ , typ)	Disabled	Operating	Operating	Operating	$V_{VCP} \geq V_{(CP\_UV)}$ ( $V_{VM} + 1.5$ , typ)
External FET overload (OCP)	$V_{DS} \geq V_{DS(OCP)}$ $V_{SP} - V_{SN} > 1$ V	Disabled	Operating	Operating	Operating	$t_{(RETRY)}$
Gate driver fault (GDF)	Gate voltage unchanged after $t_{(DRIVE)}$	Disabled	Operating	Operating	Operating	$t_{(RETRY)}$
Watchdog fault (WDFLT)	Watchdog timer expires	Disabled	Operating	Operating	Operating	CLR_FLT bit
Thermal shutdown (TSD)	$T_J \geq T_{SD}$ (150°C, min)	Disabled	Disabled	Disabled	Operating	$T_J \leq T_{SD} - T_{hys}$ ( $T_{hys}$ is typically 20°C)



### 7.3.15 Hardware Interface

The DRV8702D-Q1 hardware interface allows the device to be configured without a SPI, however not all of the functionality is configurable like the DRV8703D-Q1 device. The following configuration settings are fixed for the hardware-interface device option:

- The  $t_{off}$  value is set to 25  $\mu$ s.
- Current regulation is enabled
- The VREF pin voltage is not scaled internally (100%).
- The shunt amplifier has a fixed gain of 19.8 V/V.

#### 7.3.15.1 IDRIVE (6-level input)

The voltage or resistance on the IDRIVE pin sets the peak source and peak sink IDRIVE setting as listed in [表 9](#).

**表 9. DRV8702D-Q1 IDRIVE Settings**

IDRIVE RESISTANCE	IDRIVE VOLTAGE	SOURCE CURRENT		SINK CURRENT	
		$V_{VM} = 5.5 V$	$V_{VM} = 13.5 V$	$V_{VM} = 5.5 V$	$V_{VM} = 13.5 V$
< 1 k $\Omega$ to GND	GND	High-side: 10 mA Low-side: 10 mA	High-side: 10 mA Low-side: 10 mA	High-side: 20 mA Low-side: 20 mA	High-side: 20 mA Low-side: 20 mA
33 k $\Omega \pm 5\%$ to GND	0.7 V $\pm 5\%$	High-side: 20 mA Low-side: 20 mA	High-side: 20 mA Low-side: 20 mA	High-side: 40 mA Low-side: 40 mA	High-side: 40 mA Low-side: 40 mA
200 k $\Omega \pm 5\%$ to GND	2 V $\pm 5\%$	High-side: 50 mA Low-side: 40 mA	High-side: 50 mA Low-side: 45 mA	High-side: 90 mA Low-side: 85 mA	High-side: 95 mA Low-side: 95 mA
> 2 M $\Omega$ to GND, Hi-Z	3 V $\pm 5\%$	High-side: 145 mA Low-side: 115 mA	High-side: 155 mA Low-side: 130 mA	High-side: 250 mA Low-side: 235 mA	High-side: 265 mA Low-side: 260 mA
68 k $\Omega \pm 5\%$ to AVDD	4 V $\pm 5\%$	High-side: 190 mA Low-side: 145 mA	High-side: 210 mA Low-side: 180 mA	High-side: 330 mA Low-side: 300 mA	High-side: 350 mA Low-side: 350 mA
< 1 k $\Omega$ to AVDD	AVDD	High-side: 240 mA Low-side: 190 mA	High-side: 260 mA Low-side: 225 mA	High-side: 420 mA Low-side: 360 mA	High-side: 440 mA Low-side: 430 mA

#### 7.3.15.2 VDS (6-Level Input)

This input controls the VDS monitor trip voltage as listed in [表 10](#).

**表 10. DRV8702D-Q1 VDS Settings**

VDS RESISTANCE	VDS VOLTAGE	OVERCURRENT TRIP LEVEL ( $V_{DS(OCF)}$ )
< 1 k $\Omega$ to GND	GND	0.06 V
33 k $\Omega \pm 5\%$ to GND	0.7 V $\pm 5\%$	0.12 V
200 k $\Omega \pm 5\%$ to GND	2 V $\pm 5\%$	0.24 V
> 2 M $\Omega$ to GND, Hi-Z	3 V $\pm 5\%$	0.48 V
68 k $\Omega \pm 5\%$ to AVDD	4 V $\pm 5\%$	0.96 V
< 1 k $\Omega$ to AVDD	AVDD	Disabled

## 7.4 Device Functional Modes

The DRV870xD-Q1 device is active unless the nSLEEP pin is brought low. In sleep mode, the charge pump is disabled, the half-bridge FETs are disabled to the Hi-Z state, and the AVDD and DVDD regulators are disabled.

### 注

The  $t_{(SLEEP)}$  time must elapse after a falling edge on the nSLEEP pin before the device is in sleep mode. The DRV870xD-Q1 device is brought out of sleep mode automatically if the nSLEEP pin is brought high.

The  $t_{(WAKE)}$  time must elapse before the outputs change state after wakeup.

On the DRV8703D-Q1 device, the SPI settings are reset when coming out of UVLO or exiting sleep mode.

While the nSLEEP pin is brought low, both external half-bridge FETs are disabled. The high-side gate pin, GH, are pulled to the output node, SH, by an internal resistor and the low-side gate pin, GL, are pulled to ground.

When the VM voltage is not applied and during the power-on time ( $t_{on}$ ) the outputs are disabled using weak pulldown resistors between the GH and SH pins and the GL and GND pins.

### 注

The MODE pin controls the device-logic operation for phase and enable, independent half-bridge, or PWM input modes. This operation is latched on power up or when exiting sleep mode.

## 7.5 Programming

### 7.5.1 SPI Communication

#### 7.5.1.1 Serial Peripheral Interface (SPI)

The SPI (DRV8703D-Q1 only) is used to set device configurations, operating parameters, and read out diagnostic information. The DRV8703D-Q1 SPI operates in slave mode. The SPI input data (SDI) word consists of a 16-bit word, with a 5-bit command, 3 don't care bits, and 8 bits of data. The SPI output data (SDO) word consists of 8-bit register data and the first 8 bits are don't cares.

A valid frame has to meet following conditions:

- The clock polarity (CPOL) must be set to 0.
- The clock phase (CPHA) must be set to 0.
- The SCLK pin must be low when the nSCS pin goes low and when the nSCS pin goes high.
- No SCLK signal can occur when the nSCS signal is in transition.
- The SCLK pin must be low when the nSCS pin goes high.
- The nSCS pin should be taken high for at least 500 ns between frames.
- When the nSCS pin is asserted high, any signals at the SCLK and SDI pins are ignored, and the SDO pin is in the high impedance state.
- Full 16 SCLK cycles must occur.
- Data is captured on the falling edge of the clock and data is driven on the rising edge of the clock.
- The most-significant bit (MSB) is shifted in and out first
- For a write command, if the data word sent to the SDI pin is less than or more than 16 bits, a frame error occurs and the data word is ignored.
- For a write command, the existing data in the register being written to is shifted out on the SDO pin following the 5-bit command data

## Programming (接下页)

### 7.5.1.2 SPI Format

The SDI input-data word is 16 bits long and consists of the following format:

- 1 read or write bit, W (bit 15)
- 4 address bits, A (bits 14 through 11)
- 3 don't care bits, X (10 through 8)
- 8 data bits, D (7:0)

The SDO output-data word is 16 bits long and the first 8 bits are don't care bits. The data word is the content of the register being accessed.

For a write command ( $W0 = 0$ ), the response word on the SDO pin is the data currently in the register being written to.

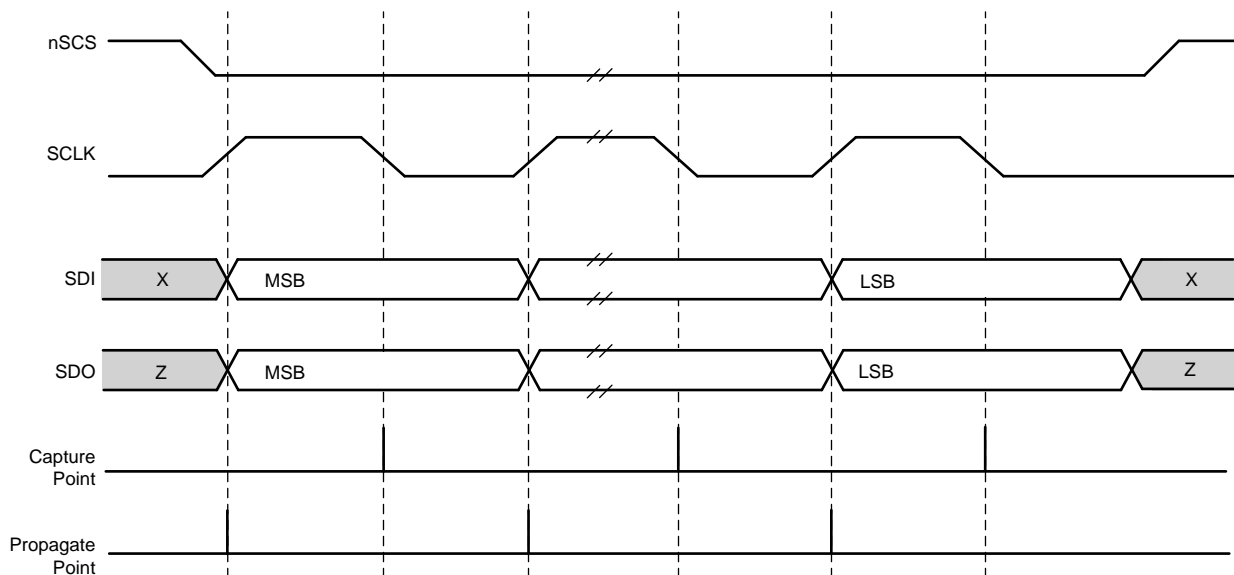
For a read command ( $W0 = 1$ ), the response word is the data currently in the register being read.

**表 11. SDI Input Data Word Format**

R/W	ADDRESS				DON'T CARE			DATA							
B15	B14	B13	B12	B11	B10	B9	B8	B7	B6	B5	B4	B3	B2	B1	B0
W0	A3	A2	A1	A0	X	X	X	D7	D6	D5	D4	D3	D2	D1	D0

**表 12. SDO Output Data Word Format**

DON'T CARE								DATA							
B15	B14	B13	B12	B11	B10	B9	B8	B7	B6	B5	B4	B3	B2	B1	B0
X	X	X	X	X	X	X	X	D7	D6	D5	D4	D3	D2	D1	D0



**图 46. SPI Transaction**

The SCLK pin should be low at power-up of the device for reliable SPI transaction. If the SCLK pin cannot be guaranteed to be low at power-up, TI recommends performing a dummy SPI-read transaction (of any register) after power-up to ensure reliable subsequent transactions. Data read from this dummy read transaction should be discarded.



## 7.6 Register Maps

**DRV8703D-Q1 Memory Map**

Register Name	7	6	5	4	3	2	1	0	Access Type	Address (Hex)	
FAULT Status	FAULT	WDFLT	GDF	OCF	VM_UVFL	VCP_UVFL	OTSD	OTW	R	0	
VDS and GDF	RESERVED		H_GDF	L_GDF	RESERVED		H_VDS	L_VDS	R	1	
Main	RESERVED		LOCK			IN1	IN2	CLR_FLT	RW	2	
IDRIVE and WD	TDEAD		WD_EN	WD_DLY		IDRIVE			RW	3	
VDS	SO_LIM	VDS		RESERVED			DIS_H_VDS	DIS_L_VDS	RW	4	
Config	TOFF		CHOP_IDS	VREF_SCL		SH_EN	GAIN_CS			RW	5

**表 13. Access Type Codes**

Access Type	Code	Description
<b>Read Type</b>		
R	R	Read
<b>Write Type</b>		
W	W	Write

### 7.6.1 Status Registers

The status registers are used to report warning and fault conditions. Status registers are read only registers.

表 14 lists the memory-mapped registers for the status registers. All register offset addresses not listed in 表 14 should be considered as reserved locations and the register contents should not be modified.

**表 14. Status Registers Summary Table**

Address	Register Name	Section
0x00h	FAULT status	<a href="#">Go</a>
0x01h	VDS and GDF status	<a href="#">Go</a>

#### 7.6.1.1 FAULT Status Register (address = 0x00h)

FAULT status is shown in 图 47 and described in 表 15.

Return to [Summary Table](#).

Read only

**图 47. FAULT Status Register**

7	6	5	4	3	2	1	0
FAULT	WDFLT	GDF	OCF	VM_UVFL	VCP_UVFL	OTSD	OTW
R-0b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b	R-0b

**表 15. FAULT Status Field Descriptions**

Bit	Field	Type	Default	Description
7	FAULT	R	0b	Logic OR of the FAULT status register excluding the OTW bit
6	WDFLT	R	0b	Watchdog time-out fault
5	GDF	R	0b	Indicates gate drive fault condition
4	OCF	R	0b	Indicates VDS monitor overcurrent fault condition
3	VM_UVFL	R	0b	Indicates VM undervoltage lockout fault condition
2	VCP_UVFL	R	0b	Indicates charge-pump undervoltage fault condition
1	OTSD	R	0b	Indicates overtemperature shutdown
0	OTW	R	0b	Indicates overtemperature warning

### 7.6.1.2 VDS and GDF Status Register Name (address = 0x01h)

VDS and GDF status is shown in [图 48](#) and described in [表 16](#).

Return to [Summary Table](#).

Read only

**图 48. VDS and GDF Status Register**

7	6	5	4	3	2	1	0
RESERVED		H_GDF	L_GDF	RESERVED		H_VDS	L_VDS
R-00b		R-0b	R-0b	R-00b		R-0b	R-0b

**表 16. VDS and GDF Status Field Descriptions**

Bit	Field	Type	Default	Description
7-6	RESERVED	R	00b	Reserved
5	H_GDF	R	0b	Indicates gate drive fault on the high-side FET of half-bridge
4	L_GDF	R	0b	Indicates gate drive fault on the low-side FET of half-bridge
3-2	RESERVED	R	00b	Reserved
1	H_VDS	R	0b	Indicates VDS monitor overcurrent fault on the high-side FET of half-bridge
0	L_VDS	R	0b	Indicates VDS monitor overcurrent fault on the low-side FET of half-bridge

### 7.6.2 Control Registers

The control registers are used to configure the device. Control registers are read and write capable.

[表 17](#) lists the memory-mapped registers for the status registers. All register offset addresses not listed in [表 17](#) should be considered as reserved locations and the register contents should not be modified.

**表 17. Status Registers Summary Table**

Address	Register Name	Section
0x02h	Main control	<a href="#">Go</a>
0x03h	IDRIVE and WD control	<a href="#">Go</a>
0x04h	VDS control	<a href="#">Go</a>
0x05h	Config control	<a href="#">Go</a>

### 7.6.2.1 Main Control Register Name (address = 0x02h)

Main control is shown in [图 49](#) and described in [表 18](#).

Return to [Summary Table](#).

Read and write

**图 49. Main Control Register**

7	6	5	4	3	2	1	0
RESERVED		LOCK			IN1	IN2	CLR_FLT
R/W-00b		R/W-011b			R/W-0b	R/W-0b	R/W-0b

**表 18. Main Control Field Descriptions**

Bit	Field	Type	Default	Description
7-6	RESERVED	R/W	00b	Reserved
5-3	LOCK	R/W	011b	Write 110b to lock the settings by ignoring further register changes except to address 0x02h. Writing any sequence other than 110b has no effect when unlocked. Write 011b to this register to unlock all registers. Writing any sequence other than 011b has no effect when locked.
2	IN1	R/W	0b	This bit is ORed with the IN1 pin
1	IN2	R/W	0b	This bit is ORed with the IN2 pin
0	CLR_FLT	R/W	0b	Write a 1 to this bit to clear the fault bits

**7.6.2.2 IDRIVE and WD Control Register Name (address = 0x03h)**

 IDRIVE and WD control is shown in [图 50](#) and described in [表 19](#).

 Return to [Summary Table](#).

Read and write

**图 50. IDRIVE and WD Register**

7	6	5	4	3	2	1	0
TDEAD		WD_EN	WD_DLY		IDRIVE		
R/W-00b		R/W-0b	R/W-00b		R/W-111b		

**表 19. IDRIVE and WD Field Descriptions**

Bit	Field	Type	Default	Description
7-6	TDEAD	R/W	00b	Dead time 00b = 120 ns 01b = 240 ns 10b = 480 ns 11b = 960 ns
5	WD_EN	R/W	0b	Time-out of the watchdog timer
4-3	WD_DLY	R/W	00b	Enables or disables the watchdog timer (disabled by default) 00b = 10 ms 01b = 20 ms 10b = 50 ms 11b = 100 ms
2-0	IDRIVE	R/W	111b	Sets the peak source current and peak sink current of the gate drive. <a href="#">表 20</a> lists the bit settings.

**表 20. IDRIVE Bit Settings**

Bit Value	Source Current		Sink Current	
	V <sub>VM</sub> = 5.5 V	V <sub>VM</sub> = 13.5 V	V <sub>VM</sub> = 5.5 V	V <sub>VM</sub> = 13.5 V
000b	High-side: 10 mA Low-side: 10 mA	High-side: 10 mA Low-side: 10 mA	High-side: 20 mA Low-side: 20 mA	High-side: 20 mA Low-side: 20 mA
001b	High-side: 20 mA Low-side: 20 mA	High-side: 20 mA Low-side: 20 mA	High-side: 40 mA Low-side: 40 mA	High-side: 40 mA Low-side: 40 mA
010b	High-side: 50 mA Low-side: 40 mA	High-side: 50 mA Low-side: 45 mA	High-side: 90 mA Low-side: 85 mA	High-side: 95 mA Low-side: 95 mA
011b	High-side: 70 mA Low-side: 55 mA	High-side: 70 mA Low-side: 60 mA	High-side: 120 mA Low-side: 115 mA	High-side: 130 mA Low-side: 125 mA
100b	High-side: 100 mA Low-side: 75 mA	High-side: 105 mA Low-side: 90 mA	High-side: 170 mA Low-side: 160 mA	High-side: 185 mA Low-side: 180 mA
101b	High-side: 145 mA Low-side: 115 mA	High-side: 155 mA Low-side: 130 mA	High-side: 250 mA Low-side: 235 mA	High-side: 265 mA Low-side: 260 mA
110b	High-side: 190 mA Low-side: 145 mA	High-side: 210 mA Low-side: 180 mA	High-side: 330 mA Low-side: 300 mA	High-side: 350 mA Low-side: 350 mA
111b	High-side: 240 mA Low-side: 190 mA	High-side: 260 mA Low-side: 225 mA	High-side: 420 mA Low-side: 360 mA	High-side: 440 mA Low-side: 430 mA

### 7.6.2.3 VDS Control Register Name (address = 0x04h)

VDS control is shown in [图 51](#) and described in [表 21](#).

Return to [Summary Table](#).

Read and write

**图 51. VDS Control Register**

7	6	5	4	3	2	1	0
SO_LIM	VDS		RESERVED		DIS_H_VDS	DIS_L_VDS	
R/W-0b	R/W-111b		R-00b		R/W-0b	R/W-0b	

**表 21. VDS Control Field Descriptions**

Bit	Field	Type	Default	Description
7	SO_LIM	R/W	0b	0b = Default operation 1b = SO output is voltage-limited to 3.6 V
6-4	VDS	R/W	111b	Sets the $V_{DS(OC)}$ monitor for each FET 000b = 0.06 V 001b = 0.145 V 010b = 0.17 V 011b = 0.2 V 100b = 0.12 V 101b = 0.24 V 110b = 0.48 V 111b = 0.96 V
3-2	RESERVED	R	00b	Reserved
1	DIS_H_VDS	R/W	0b	Disables the VDS monitor on the high-side FET of half-bridge (enabled by default)
0	DIS_L_VDS	R/W	0b	Disables the VDS monitor on the low-side FET of half-bridge (enabled by default)

#### 7.6.2.4 Config Control Register Name (address = 0x05h)

Config control is shown in [图 52](#) and described in [表 22](#).

Return to [Summary Table](#).

Read and write

**图 52. Config Control Register**

7	6	5	4	3	2	1	0
TOFF		CHOP_IDS	VREF_SCL		SH_EN	GAIN_CS	
R/W-00b		R/W-0b	R/W-00b		R/W-0b	R/W-01b	

**表 22. Config Control Field Descriptions**

Bit	Field	Type	Default	Description
7-6	TOFF	R/W	00b	Off time for PWM current chopping 00b = 25 $\mu$ s 01b = 50 $\mu$ s 10b = 100 $\mu$ s 11b = 200 $\mu$ s
5	CHOP_IDS	R/W	0b	Disables current regulation (enabled by default)
4-3	VREF_SCL	R/W	00b	Scale factor for the VREF input 00b = 100% 01b = 75% 10b = 50% 11b = 25%
2	SH_EN	R/W	0b	Enables sample and hold operation of the shunt amplifier (disabled by default)
1-0	GAIN_CS	R/W	01b	Shunt amplifier gain setting 00b = 10 V/V 01b = 19.8 V/V 10b = 39.4 V/V 11b = 78 V/V

## 8 Application and Implementation

### 注

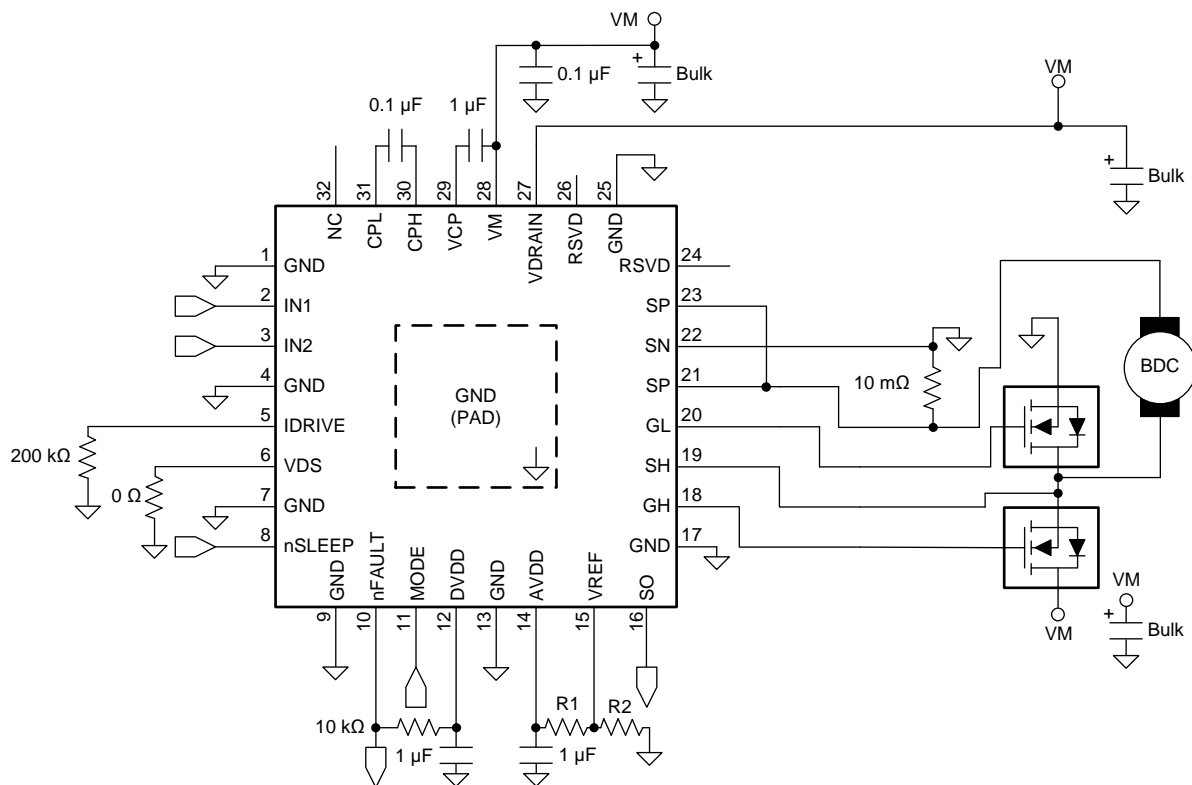
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The DRV870xD-Q1 device is used in brushed-DC, solenoid, or relay-control applications. The following typical application can be used to configure the DRV870xD-Q1 device.

### 8.2 Typical Application

This application features the DRV8702D-Q1 device.



Copyright © 2017, Texas Instruments Incorporated

图 53. DRV8702D-Q1 Typical Application Schematic

## Typical Application (接下页)

### 8.2.1 Design Requirements

For this design example, use the parameters listed in 表 23 as the input parameters.

表 23. Design Parameters

DESIGN PARAMETER	REFERENCE	EXAMPLE VALUE
Nominal supply voltage	VM	14 V
Supply voltage range		7 V to 35 V
FET part number		CSD18502Q5B
FET total gate charge	$Q_g$	52 nC (typical)
FET gate-to-drain charge	$Q_{gd}$	8.4 nC (typical)
Target FET gate rise time	$t_r$	100 to 300 ns
Motor current chopping level	$I_{(CHOP)}$	15 A

### 8.2.2 Detailed Design Procedure

#### 8.2.2.1 External FET Selection

The DRV8702D-Q1 FET support is based on the charge-pump capacity and PWM-output frequency. For a quick calculation of FET driving capacity, use 公式 3 when drive and brake (slow decay) are the primary modes of operation.

$$Q_g < \frac{I_{VCP}}{f_{(PWM)}}$$

where

- $f_{PWM}$  is the maximum desired PWM frequency to be applied to the DRV8702D-Q1 inputs or the current chopping frequency, whichever is larger.
- $I_{VCP}$  is the charge-pump capacity, which depends on the VM voltage. (3)

The internal current chopping frequency is at most equal to the PWM frequency as shown in 公式 4.

$$f_{(PWM)} < \frac{1}{t_{off} + t_{(BLANK)}} \quad (4)$$

For example, if the VM voltage of a system is 7 V ( $I_{VCP} = 8$  mA) and uses a maximum PWM frequency of 40 kHz, then the DRV8702D-Q1 device will support FETs with a  $Q_g$  up to 200 nC.

If the application requires a forced fast decay (or alternating between drive and reverse drive), use 公式 5 to calculate the maximum FET driving capacity.

$$Q_g < \frac{I_{VCP}}{2 \times f_{(PWM)}} \quad (5)$$

#### 8.2.2.2 IDRIVE Configuration

The IDRIVE current is selected based on the gate charge of the FETs. The IDRIVE pin must be configured so that the FET gates are charged entirely during the  $t_{(DRIVE)}$  time. If the selected IDRIVE current is too low for a given FET, then the FET may not turn on completely. TI recommends adjusting these values in-system with the required external FETs and motor to determine the best possible setting for any application.

For FETs with a known gate-to-drain charge ( $Q_{gd}$ ) and desired rise time ( $t_r$ ), the IDRIVE current can be selected based on the 公式 6.

$$I_{DRIVE} > \frac{Q_{gd}}{t_r} \quad (6)$$



If the gate-to-drain charge is 2.3 nC and the desired rise time is around 100 to 300 ns, use [公式 7](#) to calculate the minimum IDRIVE ( $I_{DRIVE1}$ ) and [公式 8](#) to calculate the maximum IDRIVE ( $I_{DRIVE2}$ ).

$$I_{DRIVE1} = 8.4 \text{ nC} / 100 \text{ ns} = 84 \text{ mA} \quad (7)$$

$$I_{DRIVE2} = 8.4 \text{ nC} / 300 \text{ ns} = 28 \text{ mA} \quad (8)$$

Select a value for IDRIVE between 28 and 84 mA. An IDRIVE value of approximately 50 mA for the source (approximately 100 mA sink) was selected for this application. This value requires a 200-k $\Omega$  resistor from the IDRIVE pin to ground.

### 8.2.2.3 VDS Configuration

The VDS monitor is configured based on the maximum current and  $R_{DS(on)}$  of the FETs. The VDS pin of the DRV8702D-Q1 selects the VDS monitor trip threshold. Use [公式 3](#) to calculate the trip current.

$$I_{VDS} > \frac{V_{VDS}}{R_{DS(on)}} \quad (9)$$

If the  $R_{DS(on)}$  of the FET is 1.8 m $\Omega$  and the desired VDS trip is less than 100 A, the  $V_{VDS}$  voltage is equal to 180 mV as shown in [公式 10](#).

$$V_{VDS} = I_{VDS} \times R_{DS(on)} = 100 \text{ A} \times 1.8 \text{ m}\Omega = 180 \text{ mV} \quad (10)$$

Select a value for the VDS voltage that less than 180 mV. A  $V_{VDS}$  value of 0.12 V was selected for this application. This value requires tying the VDS pin to ground.

### 8.2.2.4 Current Chopping Configuration

The chopping current is set based on the sense resistor value and the analog voltage at the VREF pin. Use [公式 11](#) to calculate the current ( $I_{CHOP}$ ). The amplifier gain,  $A_V$ , is 19.8 V/V for the DRV8702D-Q1 and  $V_{IO}$  is typically 2.5 mV (input referred).

$$I_{CHOP} = \frac{V_{VREF} - V_{IO}}{A_V \times R_{(SENSE)}} \quad (11)$$

For example, if the desired chopping current is 15 A, select a value of 10 m $\Omega$  for  $R_{(SENSE)}$ . The value of  $V_{VREF}$  must therefore be 3.05 V. Add a resistor divider from the AVDD (5 V) pin to set the  $V_{VREF}$  at approximately 3.05 V. Select a value of 13 k $\Omega$  for and 20 k $\Omega$  for R1.

### 8.2.3 Application Curves

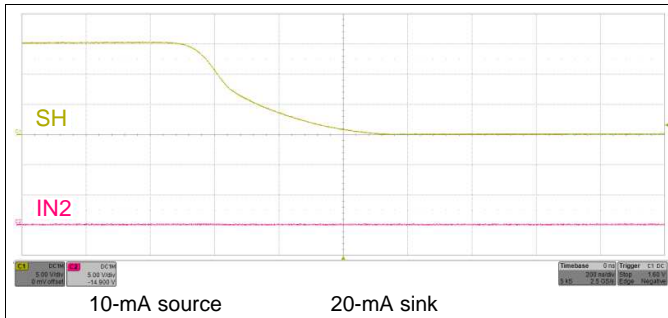


图 54. SH Fall Time

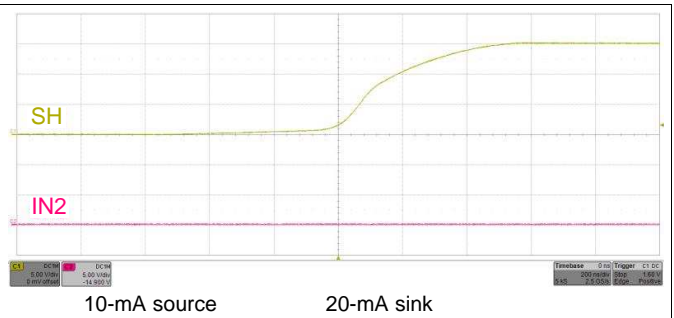


图 55. SH Rise Time

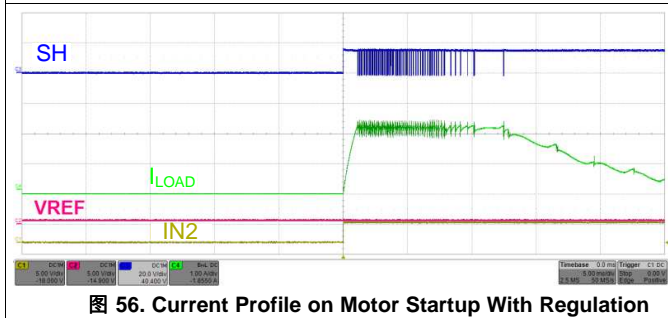


图 56. Current Profile on Motor Startup With Regulation

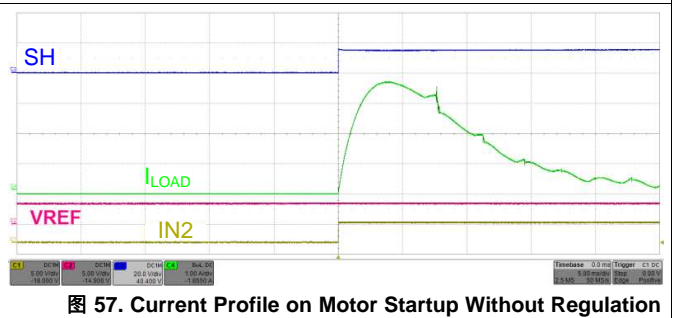


图 57. Current Profile on Motor Startup Without Regulation

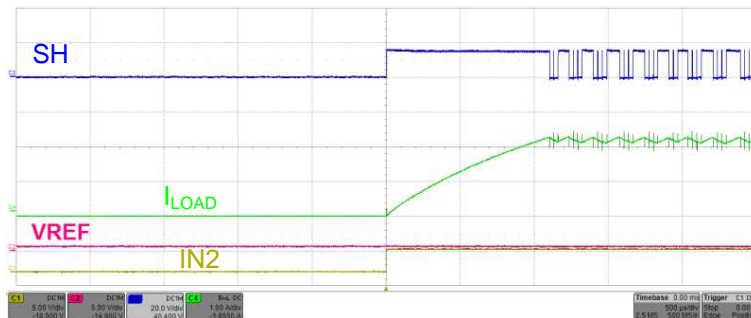


图 58. Current Regulating at 2.25 A on Motor Startup

## 9 Power Supply Recommendations

The DRV8702D-Q1 device is designed to operate with an input voltage supply (VM) range from 5.5 V to 45 V. A 0.1- $\mu\text{F}$  ceramic capacitor rated for VM must be placed as close to the DRV8702D-Q1 device as possible. Also, a bulk capacitor valued at least 10  $\mu\text{F}$  must be placed on the VM pin.

Additional bulk capacitance is required to bypass the external half-bridge FETs.

### 9.1 Bulk Capacitance Sizing

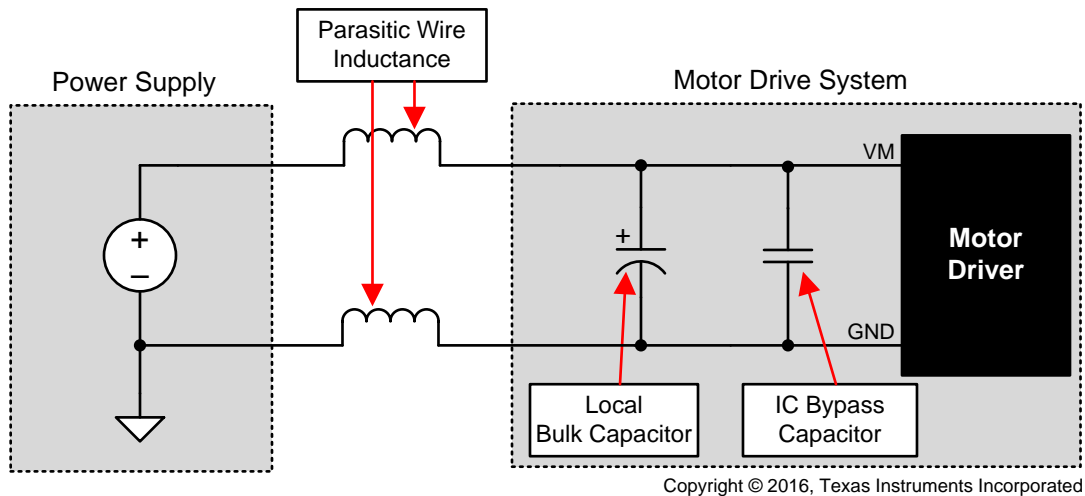
Bulk capacitance sizing is an important factor in motor drive system design. It is beneficial to have more bulk capacitance, while the disadvantages are increased cost and physical size.

The amount of local capacitance needed depends on a variety of factors including:

- The highest current required by the motor system.
- The capacitance of the power supply and the ability of the power supply to source current.
- The amount of parasitic inductance between the power supply and motor system.
- The acceptable voltage ripple.
- The type of motor used (brushed DC, brushless DC, and stepper).
- The motor braking method.

The inductance between the power supply and motor drive system limits the rate that current can change from the power supply. If the local bulk capacitance is too small, the system responds to excessive current demands or dumps from the motor with a change in voltage. When sufficient bulk capacitance is used, the motor voltage remains stable, and high current can be quickly supplied.

The data sheet provides a recommended value, but system-level testing is required to determine the appropriate sized bulk capacitor.



Copyright © 2016, Texas Instruments Incorporated

图 59. Example Setup of Motor Drive System With External Power Supply

The voltage rating for bulk capacitors should be higher than the operating voltage to provide a margin for cases when the motor transfers energy to the supply.

## 10 Layout

### 10.1 Layout Guidelines

The VM pin should be bypassed to ground using a low-ESR ceramic bypass capacitor with a recommended value of 0.1  $\mu\text{F}$  rated for VM. This capacitor should be placed as close to the VM pin as possible with a thick trace or ground-plane connection to the GND pin of the device. The VM pin must also be bypassed to ground using a bulk capacitor rated for VM. This capacitor can be electrolytic and must be at least 10  $\mu\text{F}$ .

A low-ESR ceramic capacitor must be placed between the CPL and CPH pins. A value of 0.1  $\mu\text{F}$  rated for VM is recommended. Place this capacitor as close to the pins as possible. A low-ESR ceramic capacitor must be placed in between the VM and VCP pins. A value of 1  $\mu\text{F}$  rated for 16 V is recommended. Place this component as close to the pins as possible.

Bypass the AVDD and DVDD pins to ground with ceramic capacitors rated for 6.3 V. Place these bypassing capacitors as close to the pins as possible.

Use separate traces to connect the SP and SN pins to the  $R_{(\text{SENSE})}$  resistor.

### 10.2 Layout Example

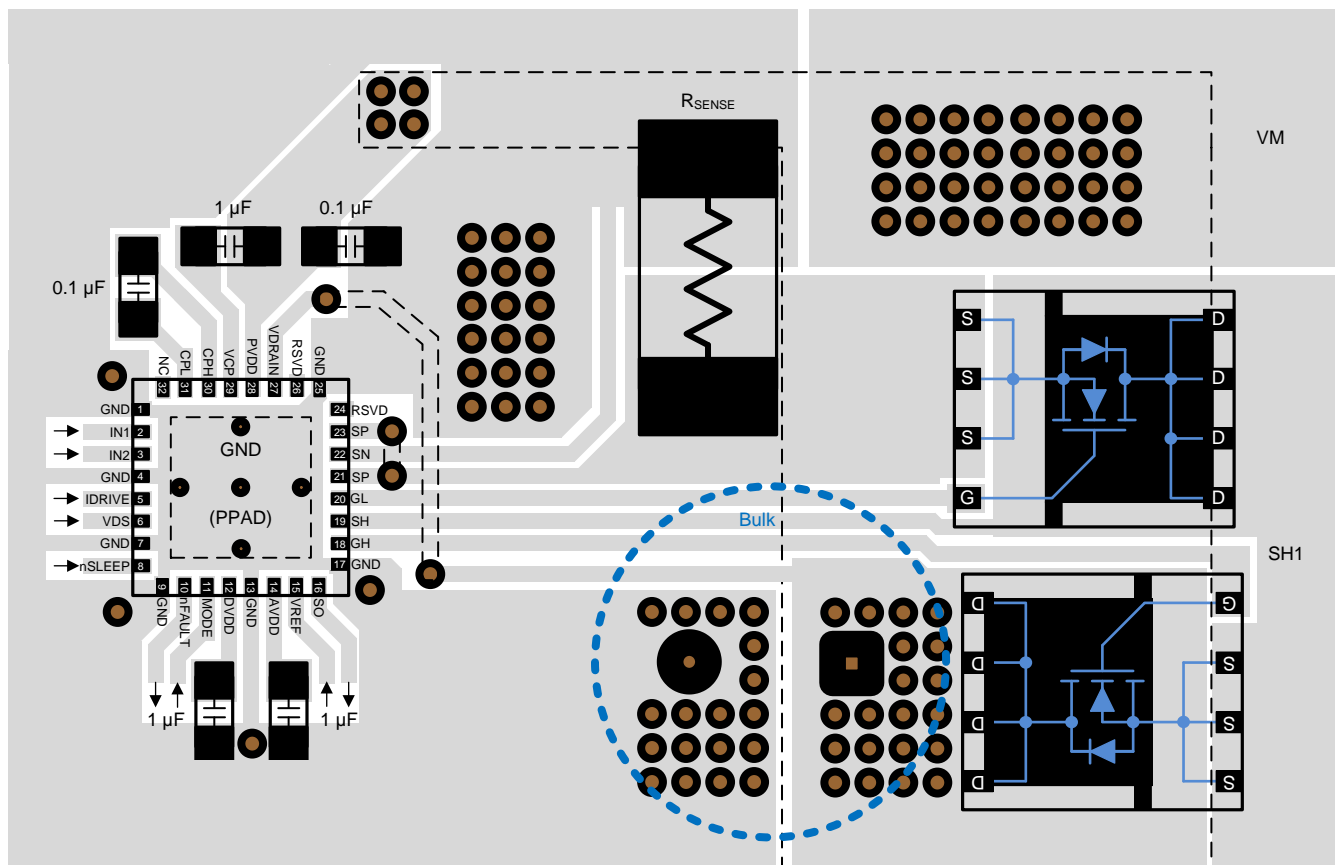


图 60. DRV8702D-Q1 Layout Example

## 11 器件和文档支持

### 11.1 文档支持

#### 11.1.1 相关文档

相关文档请参阅以下部分：

- [《用智能栅极驱动器驱动单向刷式直流电机》](#)
- [《DRV8702-Q1 EVM 用户指南》](#)
- [《DRV8703-Q1 EVM 用户指南》](#)
- [《小型电机驱动器天窗模块设计指南》](#)

#### 11.2 相关链接

下面的表格列出了快速访问链接。范围包括技术文档、支持与社区资源、工具和软件，并且可以快速访问样片或购买链接。

表 24. 相关链接

器件	产品文件夹	立即订购	技术文档	工具与软件	支持与社区
DRV8702D-Q1	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>
DRV8703D-Q1	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>

#### 11.3 接收文档更新通知

如需接收文档更新通知，请访问 [www.ti.com.cn](http://www.ti.com.cn) 网站上的器件产品文件夹。点击右上角的提醒我 (Alert me) 注册后，即可每周定期收到已更改的产品信息。有关更改的详细信息，请查阅已修订文档中包含的修订历史记录。

#### 11.4 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

**TI E2E™ Online Community** *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At [e2e.ti.com](http://e2e.ti.com), you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 11.5 商标

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

#### 11.6 静电放电警告



ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

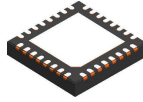
#### 11.7 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 12 机械、封装和可订购信息

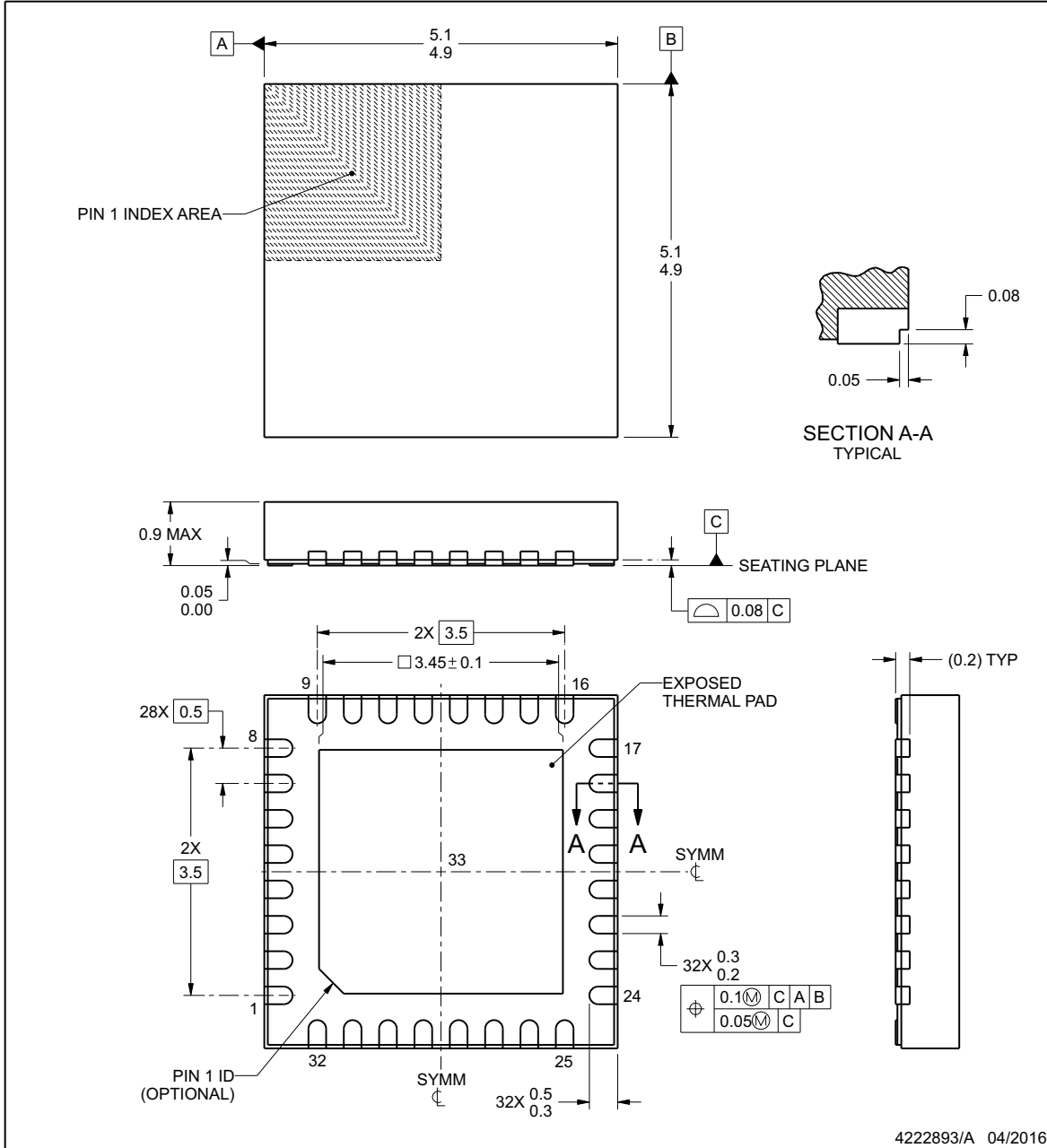
以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。



RHB0032N

PACKAGE OUTLINE  
VQFN - 0.9 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES:

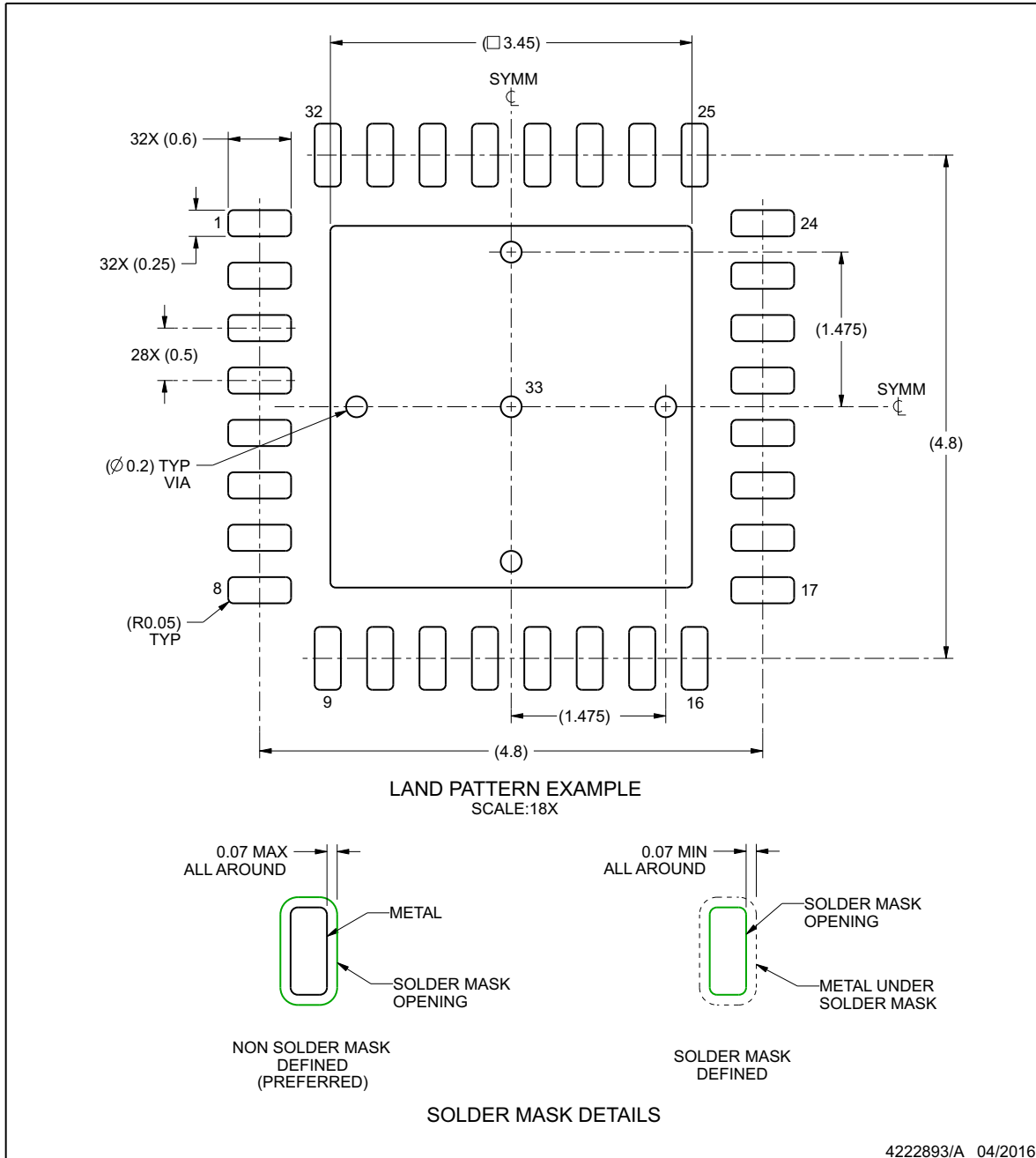
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

**EXAMPLE BOARD LAYOUT**

**RHB0032N**

**VQFN - 0.9 mm max height**

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

- This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 ([www.ti.com/lit/slua271](http://www.ti.com/lit/slua271)).
- Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.

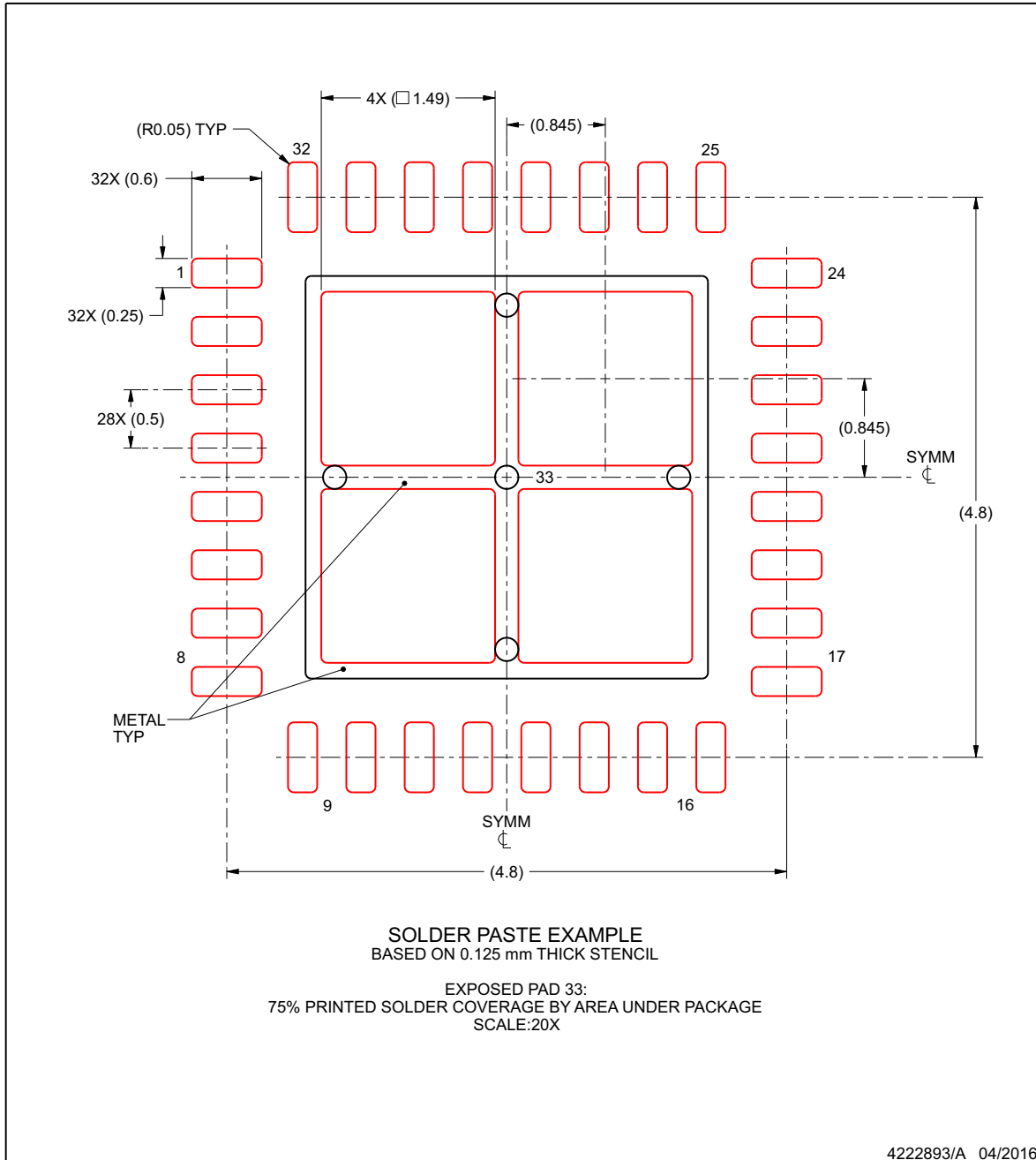


## EXAMPLE STENCIL DESIGN

**RHB0032N**

**VQFN - 0.9 mm max height**

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

## 12.1 Package Option Addendum

### 12.1.1 Packaging Information

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/Ball Finish <sup>(3)</sup>	MSL Peak Temp <sup>(4)</sup>	Op Temp (°C)	Device Marking <sup>(5)(6)</sup>
DRV8702DQRHBRQ1	PREVIEW	VQFN	RHB	32	3000	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 125	
DRV8702DQRHBTQ1	PREVIEW	VQFN	RHB	32	250	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 125	
DRV8703DQRHBRQ1	PREVIEW	VQFN	RHB	32	3000	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 125	
DRV8703DQRHBTQ1	PREVIEW	VQFN	RHB	32	250	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 125	

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PRE\_PROD** Unannounced device, not in production, not available for mass market, nor on the web, samples not available.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

(4) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

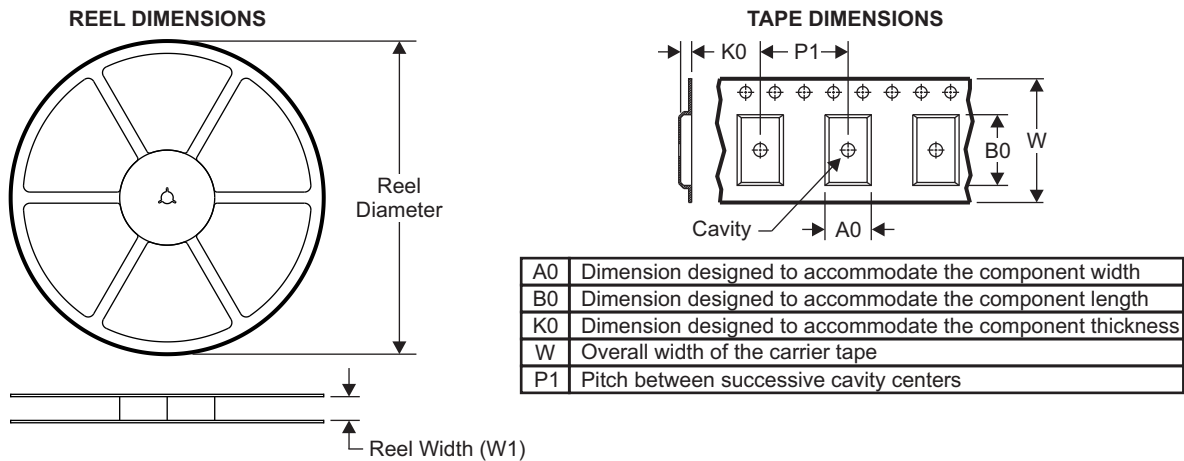
(5) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device

(6) Multiple Device markings will be inside parentheses. Only on Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

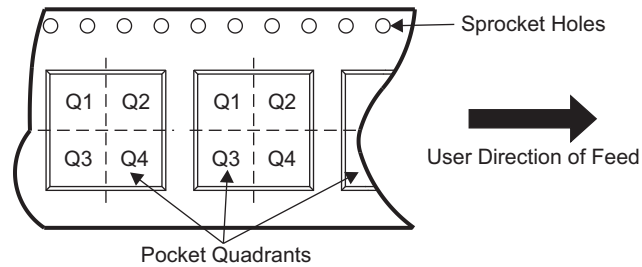
**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

### 12.1.2 Tape and Reel Information



#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV8702DQRHBTQ1	VQFN	RHB	32	250	180.0	12.4	5.25	5.25	1.1	8.0	12.0	Q2

**DRV8702D-Q1, DRV8703D-Q1**

ZHCSG57 – MARCH 2017

[www.ti.com.cn](http://www.ti.com.cn)
**TAPE AND REEL BOX DIMENSIONS**


Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV8702DQRHBTQ1	VQFN	RHB	32	250	195.0	200.0	45.0

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DRV8702DQRHBRQ1	ACTIVE	VQFN	RHB	32	3000	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 125	8702D	<a href="#">Samples</a>
DRV8702DQRHBTQ1	ACTIVE	VQFN	RHB	32	250	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 125	8702D	<a href="#">Samples</a>
DRV8703DQRHBRQ1	ACTIVE	VQFN	RHB	32	3000	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 125	8703D	<a href="#">Samples</a>
DRV8703DQRHBTQ1	ACTIVE	VQFN	RHB	32	250	Green (RoHS & no Sb/Br)	CU SN	Level-3-260C-168 HR	-40 to 125	8703D	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and

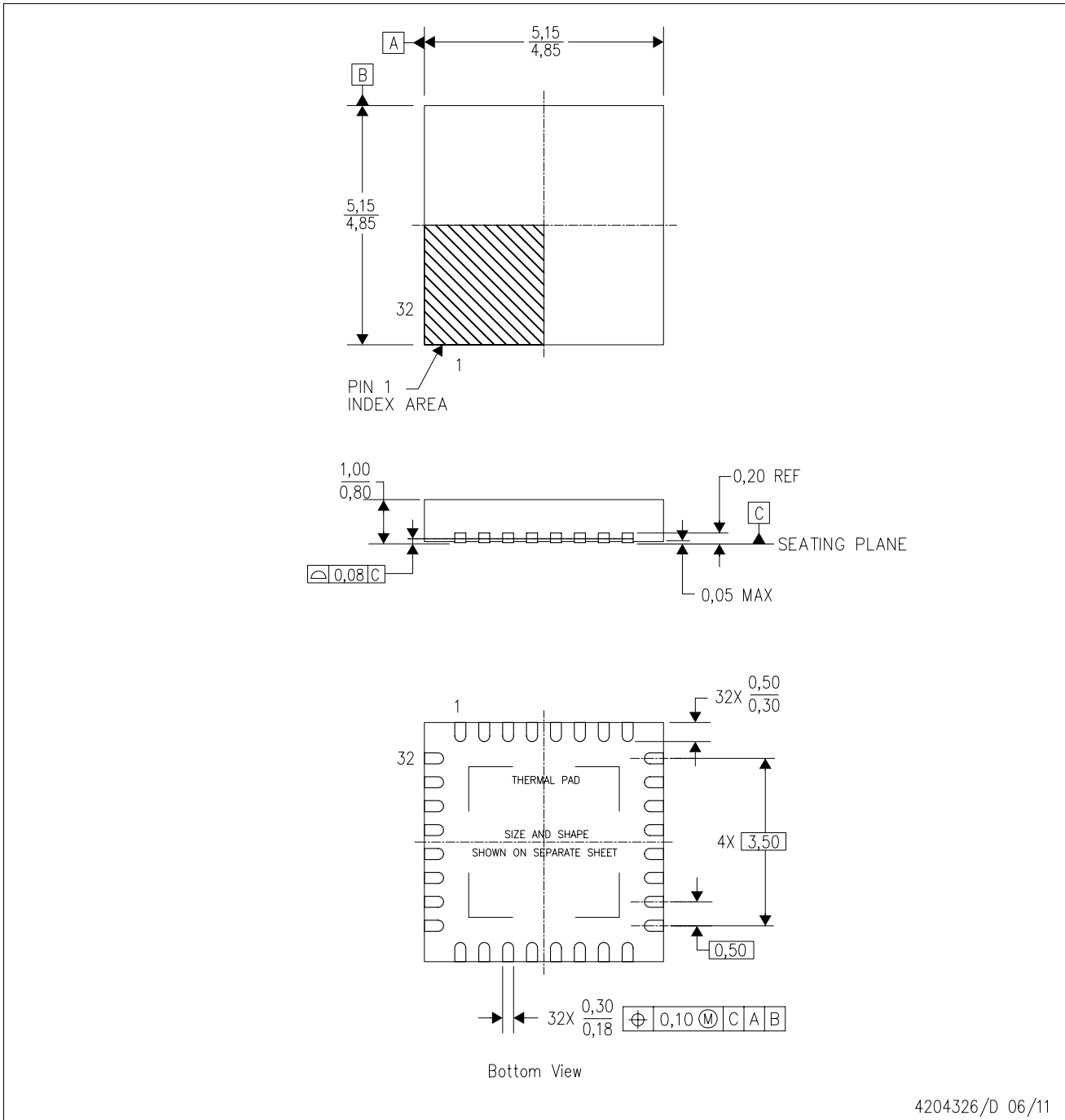
continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

# MECHANICAL DATA

RHB (S-PVQFN-N32)

PLASTIC QUAD FLATPACK NO-LEAD



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. QFN (Quad Flatpack No-Lead) Package configuration.
  - D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
  - E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
  - F. Falls within JEDEC MO-220.

## 重要声明

德州仪器 (TI) 公司有权按照最新发布的 JESD46 对其半导体产品和服务进行纠正、增强、改进和其他修改，并不再按最新发布的 JESD48 提供任何产品和服务。买方在下订单前应获取最新的相关信息，并验证这些信息是否完整且是最新的。

TI 公布的半导体产品销售条款 (<http://www.ti.com/sc/docs/stdterms.htm>) 适用于 TI 已认证和批准上市的已封装集成电路产品的销售。另有其他条款可能适用于其他类型 TI 产品及服务的使用或销售。

复制 TI 数据表上 TI 信息的重要部分时，不得变更该等信息，且必须随附所有相关保证、条件、限制和通知，否则不得复制。TI 对该等复制文件不承担任何责任。第三方信息可能受到其它限制条件的制约。在转售 TI 产品或服务时，如果存在对产品或服务参数的虚假陈述，则会失去相关 TI 产品或服务的明示或暗示保证，且构成不公平的、欺诈性商业行为。TI 对此类虚假陈述不承担任何责任。

买方和在系统中整合 TI 产品的其他开发人员（总称“设计人员”）理解并同意，设计人员在设计应用时应自行实施独立的分析、评价和判断，且应全权负责并确保应用的安全性，及设计人员的应用（包括应用中使用的 TI 产品）应符合所有适用的法律法规及其他相关要求。设计人员就自己设计的应用声明，其具备制订和实施下列保障措施所需的一切必要专业知识，能够 (1) 预见故障的危险后果，(2) 监视故障及其后果，以及 (3) 降低可能导致危险的故障几率并采取适当措施。设计人员同意，在使用或分发包含 TI 产品的任何应用前，将彻底测试该等应用和该等应用中所用 TI 产品的功能。

TI 提供技术、应用或其他设计建议、质量特点、可靠性数据或其他服务或信息，包括但不限于与评估模块有关的参考设计和材料（总称“TI 资源”），旨在帮助设计人员开发整合了 TI 产品的应用，如果设计人员（个人，或如果是代表公司，则为设计人员的公司）以任何方式下载、访问或使用任何特定的 TI 资源，即表示其同意仅为该等目标，按照本通知的条款使用任何特定 TI 资源。

TI 所提供的 TI 资源，并未扩大或以其他方式修改 TI 对 TI 产品的公开适用的质保及质保免责声明；也未导致 TI 承担任何额外的义务或责任。TI 有权对其 TI 资源进行纠正、增强、改进和其他修改。除特定 TI 资源的公开文档中明确列出的测试外，TI 未进行任何其他测试。

设计人员只有在开发包含该等 TI 资源所列 TI 产品的应用时，才被授权使用、复制和修改任何相关 TI 资源。但并未依据禁止反言原则或其他法律授予您任何 TI 知识产权的任何其他明示或默示的许可，也未授予您 TI 或第三方的任何技术或知识产权的许可，该等许可包括但不限于任何专利权、版权、屏蔽作品权或与美国 TI 产品或服务的任何整合、机器制作、流程相关的其他知识产权。涉及或参考了第三方产品或服务的信息不构成使用此类产品或服务的许可或与其相关的保证或认可。使用 TI 资源可能需要您向第三方获得对该等第三方专利或其他知识产权的许可。

TI 资源系“按原样”提供。TI 兹免除对资源及其使用作出所有其他明确或默示的保证或陈述，包括但不限于对准确性或完整性、产权保证、无屡发故障保证，以及适销性、适合特定用途和不侵犯任何第三方知识产权的任何默认保证。TI 不负责任何申索，包括但不限于因组合产品所致或与之有关的申索，也不为或对设计人员进行辩护或赔偿，即使该等产品组合已列于 TI 资源或其他地方。对因 TI 资源或其使用引起或与之有关的任何实际的、直接的、特殊的、附带的、间接的、惩罚性的、偶发的、从属或惩戒性损害赔偿，不管 TI 是否获悉可能会产生上述损害赔偿，TI 概不负责。

除 TI 已明确指出特定产品已达到特定行业标准（例如 ISO/TS 16949 和 ISO 26262）的要求外，TI 不对未达到任何该等行业标准要求而承担任何责任。

如果 TI 明确宣称产品有助于功能安全或符合行业功能安全标准，则该等产品旨在帮助客户设计和创作自己的符合相关功能安全标准和要求的的应用。在应用内使用产品的行为本身不会配有安全特性。设计人员必须确保遵守适用于其应用的相关安全要求和标准。设计人员不可将任何 TI 产品用于关乎性命的医疗设备，除非已由各方获得授权的管理人员签署专门的合同对此类应用专门作出规定。关乎性命的医疗设备是指出现故障会导致严重身体伤害或死亡的医疗设备（例如生命保障设备、心脏起搏器、心脏除颤器、人工心脏泵、神经刺激器以及植入设备）。此类设备包括但不限于，美国食品药品监督管理局认定为 III 类设备的设备，以及在美国以外的其他国家或地区认定为同等类别设备的所有医疗设备。

TI 可能明确指定某些产品具备某些特定资格（例如 Q100、军用级或增强型产品）。设计人员同意，其具备一切必要专业知识，可以为自己的应用选择适合的产品，并且正确选择产品的风险由设计人员承担。设计人员单方面负责遵守与该等选择有关的所有法律或监管要求。

设计人员同意向 TI 及其代表全额赔偿因其不遵守本通知条款和条件而引起的任何损害、费用、损失和/或责任。

邮寄地址：上海市浦东新区世纪大道 1568 号中建大厦 32 楼，邮政编码：200122  
Copyright © 2017 德州仪器半导体技术（上海）有限公司